

Cathode Physics Welcome and Electron Sources

Matt Poelker and John Smedley



Course Plan

| | Monday | Tuesday | Wednesday | Thursday | Friday |
|-------------|---|----------------------------------|---|--------------------------|-----------------------------------|
| 9:00-10:20 | Welcome Electron sources (John) | Photocathode Theory (John) | PEA Semiconductors (John) | Lasers (John) | Practical Experience (Matt) |
| 10:30-12:00 | Introduction (Photocathodes) (John) | Metal Photocathodes (John) | Materials science techniques (John) | Student presentations | Practical Experience (Matt) |
| 13:00-14:30 | Motivation for Spin Polarization (Matt) | Guns (Matt) | Diamond Amplifier (John) | Student presentations | |
| 14:40-16:00 | GaAs (Matt) | Guns (Matt) | Vacuum (Matt) | Student presentations | |

Homework will be handed out each morning and collected the next morning. The course “grade” will be $\frac{1}{2}$ homework and $\frac{1}{2}$ presentation. We want and expect everyone to succeed!

Student Presentations

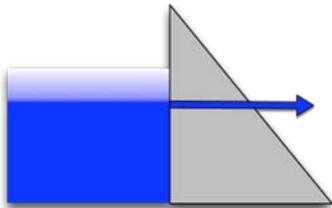
- Each student will give a 15 min presentation on a cathode related topic
- It can be from your own work, or you can present and discuss a paper in the field
- If you need ideas, Matt and I will be happy to suggest some quintessential papers
- Please see one of us during a break or in the study session and let us know what you intend to talk about, so we can make up a schedule for Thursday.

What is a Cathode?

- For our purposes, it is anything that emits electrons into vacuum in a controllable way
- Electrons are bound to materials and we must add energy to get them to escape
 - For now, think of this as adding energy required to separate a charge from its image
- For solids, there are three main ways to do this:
 - Thermionic
 - Field emission or “tunneling”
 - Photoemission
- It is possible to use a gas/plasma as an electron source as well (*student topic?*)

The Canonical Emission Equations

(slide courtesy of Dr. K. Jensen, Naval Research Laboratory)

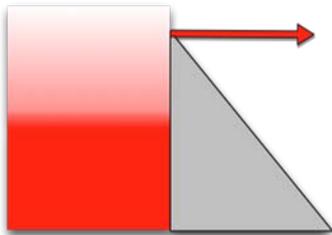


- **Field Emission**

- **Fowler Nordheim**

- E.L. Murphy, and R.H. Good,
Physical Review 102, 1464 (1956).

$$J_{FN}(F) = A_{FN} F^2 \exp\left(-\frac{B\Phi^{3/2}}{F}\right)$$

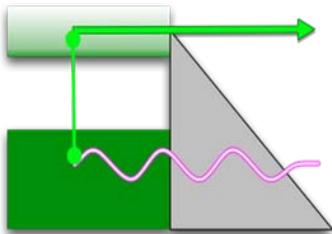


- **Thermal Emission**

- **Richardson-Laue-Dushman**

- C. Herring, and M. Nichols,
Reviews of Modern Physics 21, 185
(1949).

$$J_{RLD}(T) = A_{RLD} T^2 \exp\left(-\frac{\Phi}{k_B T}\right)$$



- **Photoemission**

- **Fowler-Dubridge**

- L.A. DuBridge
Physical Review 43, 0727 (1933).

$$J_{MFD}(\lambda) = \frac{q}{\hbar\omega} (1-R) F_\lambda(\omega) \{\hbar\omega - \Phi\}^2 I_\lambda$$

Listed chronologically

Cathode Applications– Small Electron Guns

Thermionic guns with relatively low energy are common in a number commercial applications

- Electron beam welding
- Electron beam heating
- Electron beam evaporation
 - These require 0.1 to 1 A, and generally operate at tens of kW
- Electron beam lithography
- Cathode ray tubes

Several research techniques:

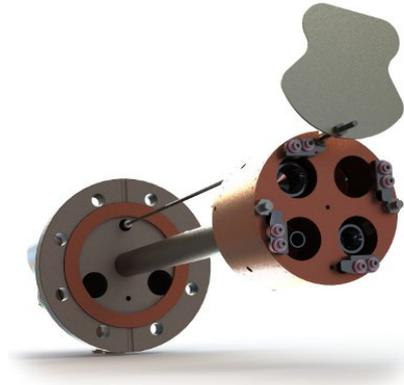
- Electron Diffraction (LEED and RHEED)
- Flood guns for charge neutralization
- Ionization of material for mass spectrometry



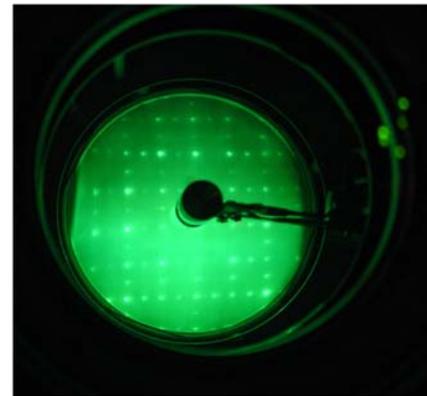
Cathode Ray Tube



Electron Gun



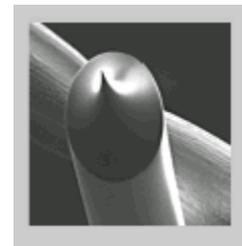
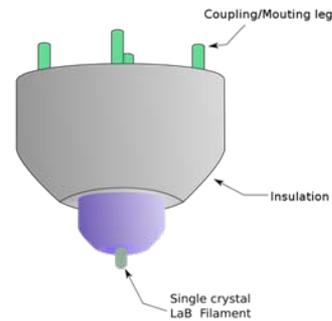
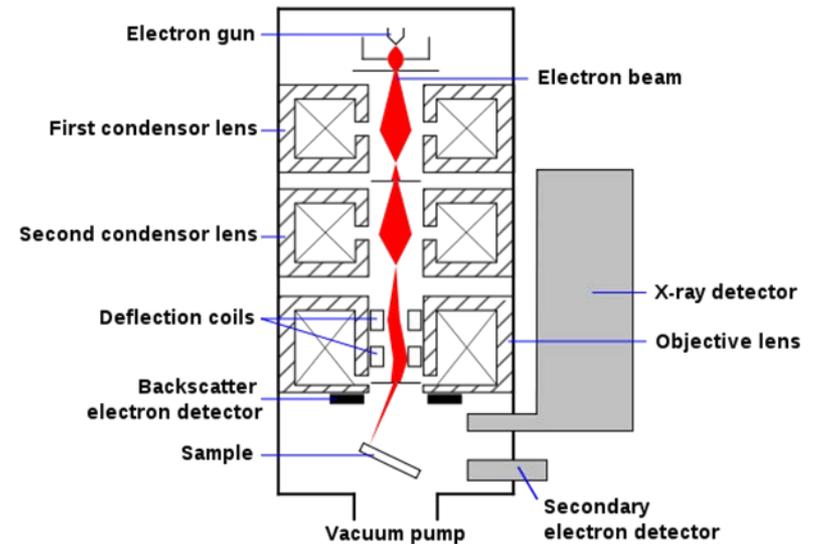
Electron Beam Evaporator



Low Energy Electron Diffraction on Si

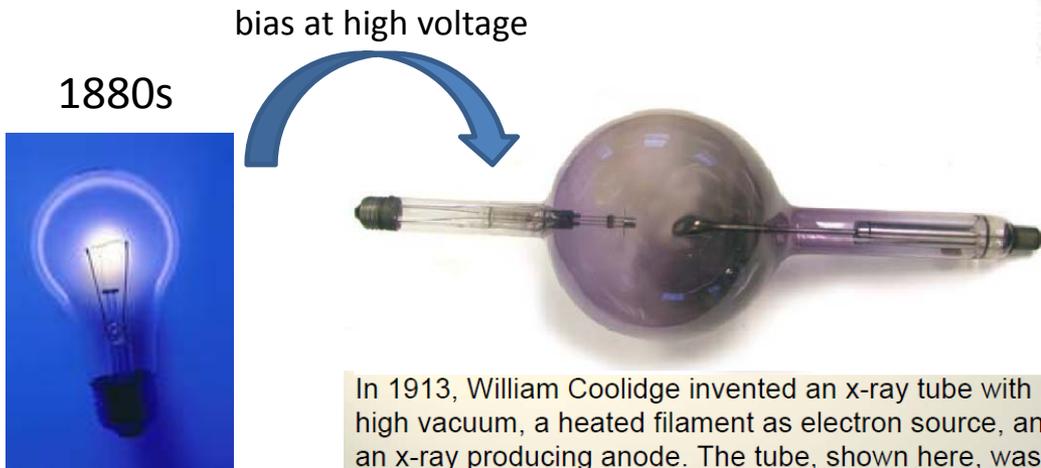
Cathode Applications– Electron Microscopes

- Thermionic & Field Emission
 - Which provides better resolution?
- Typically few μA of DC current:
 - <50 keV in a Scanning Electron Microscope (SEM)
 - <300 keV for Transmission Electron Microscope (TEM)
- PEEMs (Photoemission Electron Microscopes) are a special breed, as the photocathode *is* the sample
- Electron microscopes can be fitted with a variety of tools:
 - Nano patterning
 - Electron diffraction imaging
 - X-ray fluorescence imaging
- HW problem – estimate the resolution of a 300 keV TEM



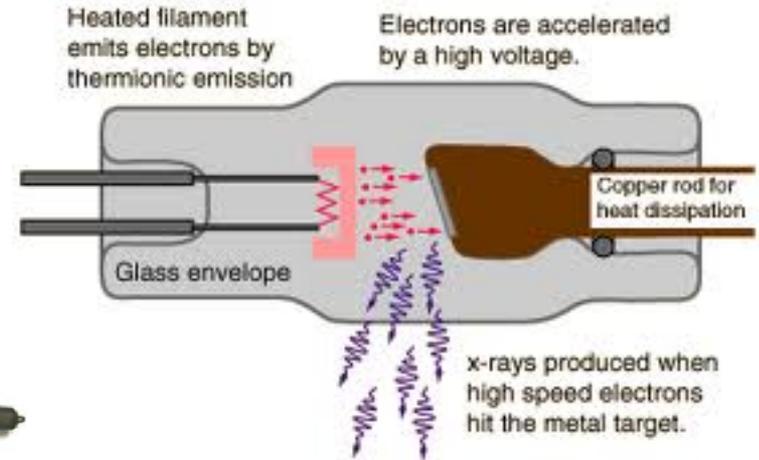
Cathode Applications— X-ray tubes

Used to make x-ray light....

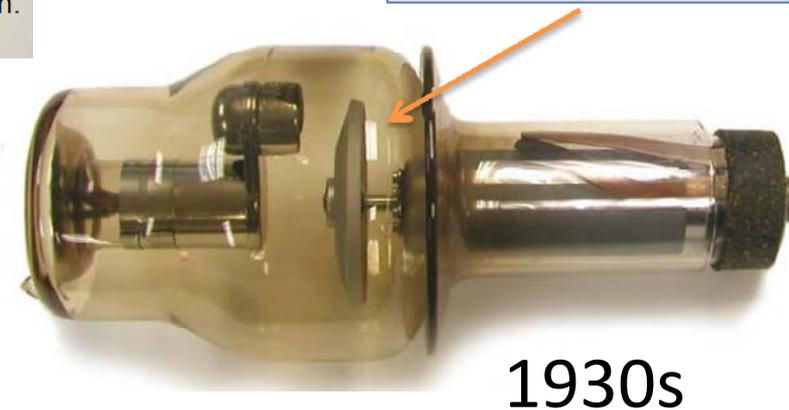


In 1913, William Coolidge invented an x-ray tube with high vacuum, a heated filament as electron source, and an x-ray producing anode. The tube, shown here, was produced in the 1920s by General Electric Corporation.

Photo: www.orau.org Oak Ridge Associated Universities

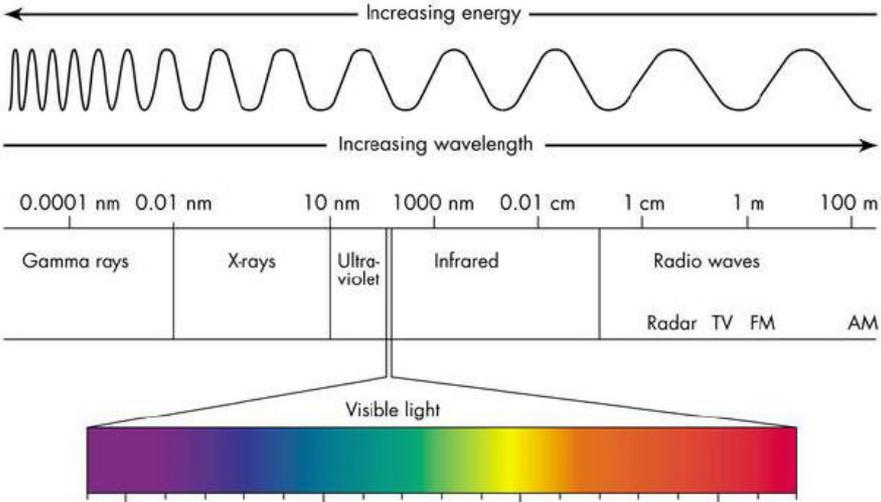


Rotating anode to distribute heat

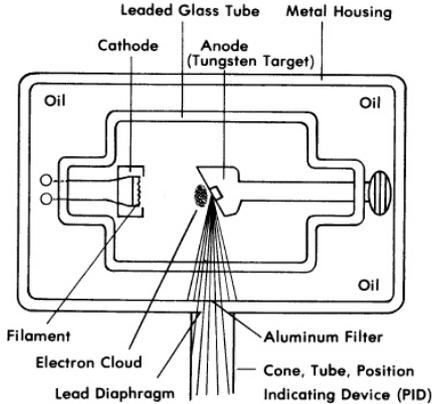
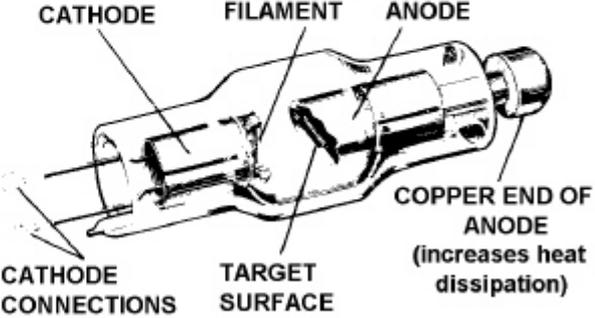
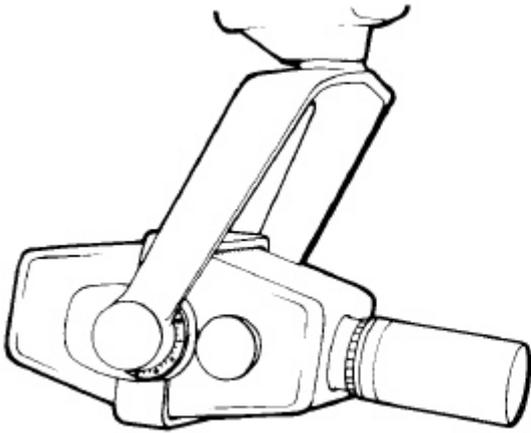


X-rays are generated when a DC electron beam, typically a few mA, strikes a tungsten target at 60-200 keV. e-Beam quality is not a big concern

Modern X-Ray Sources



X-Ray energy depends on electron beam energy, i.e., bias voltage



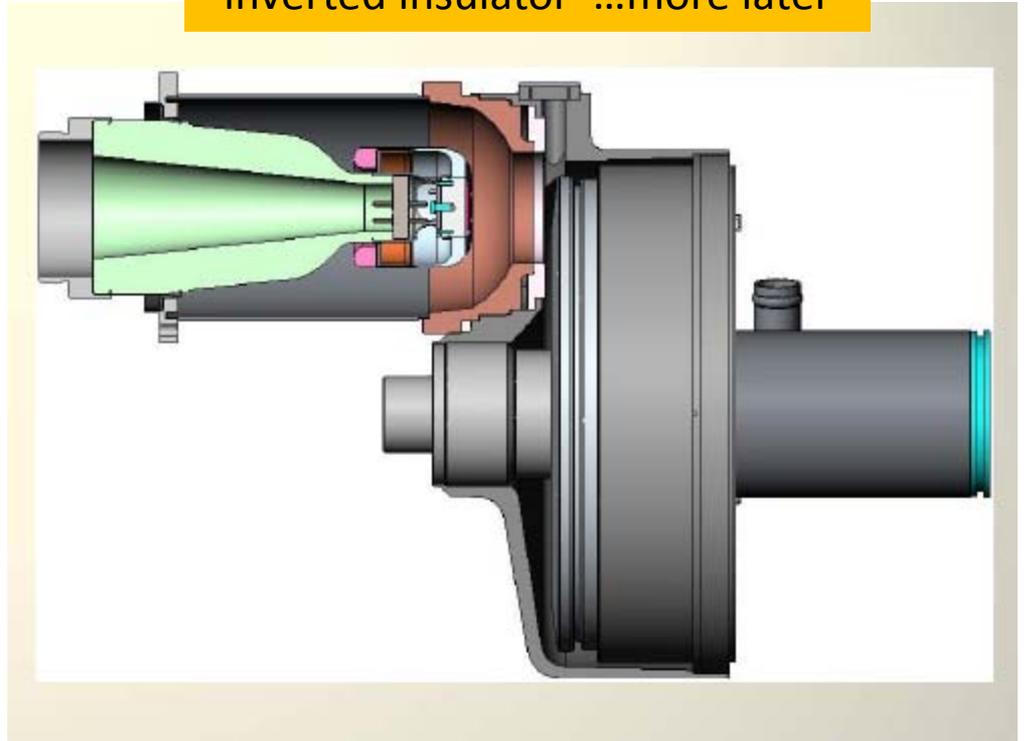
Modern X-Ray Sources

Higher e-beam current....
Higher x-ray flux



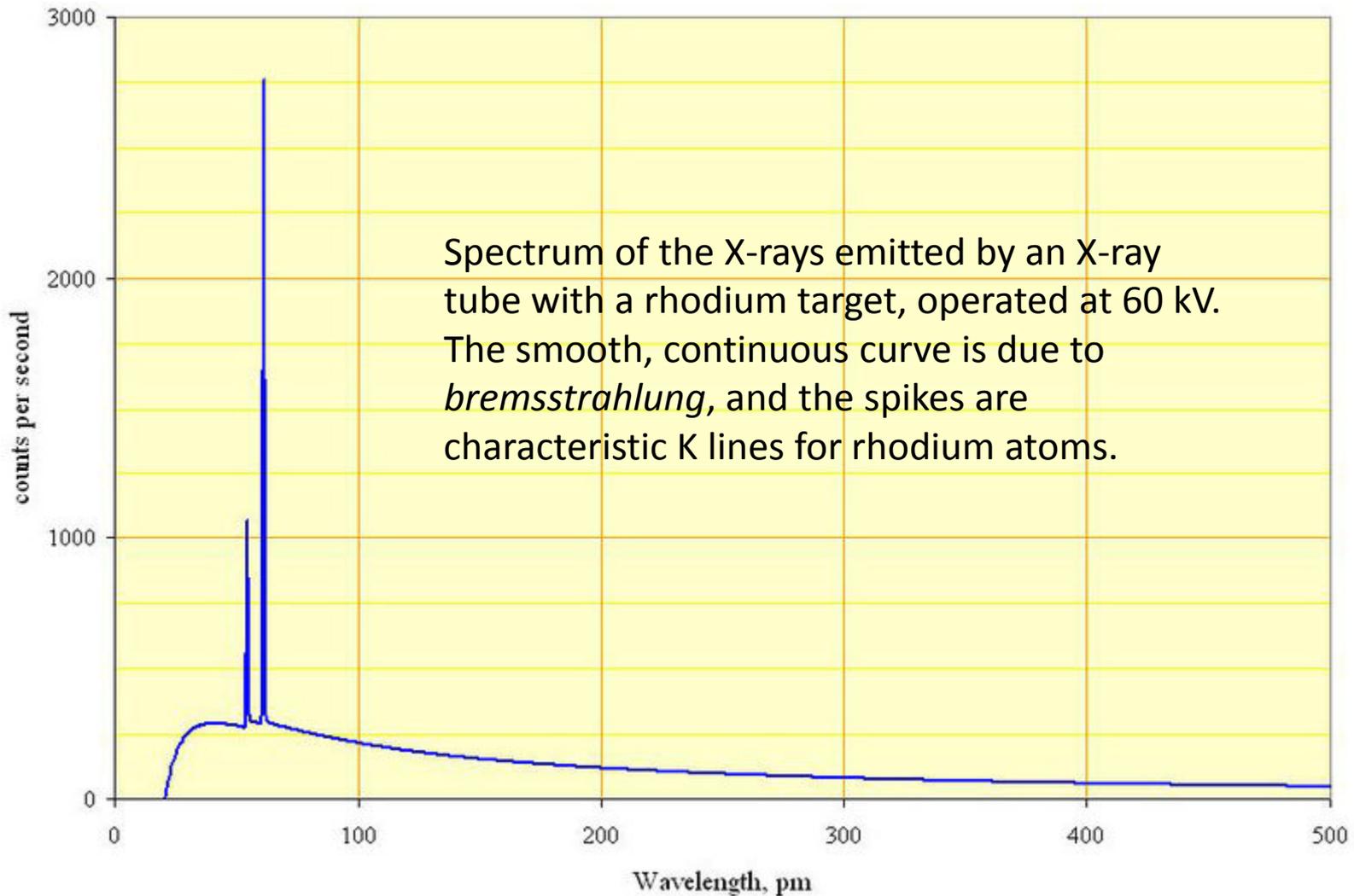
Higher Voltage....
More penetrating
x-ray beam

“inverted insulator” ...more later



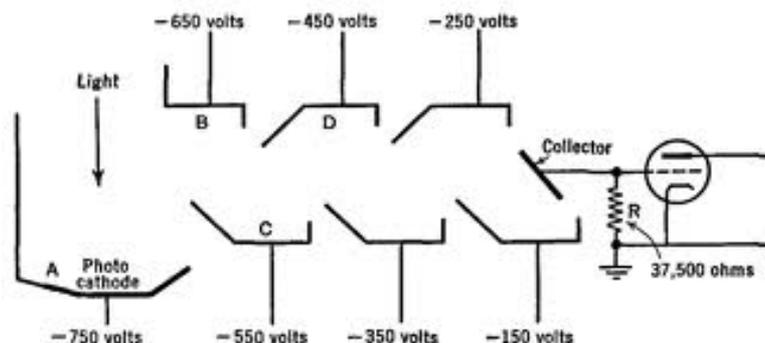
Courtesy Varian

Bremsstrahlung and Characteristic X-rays

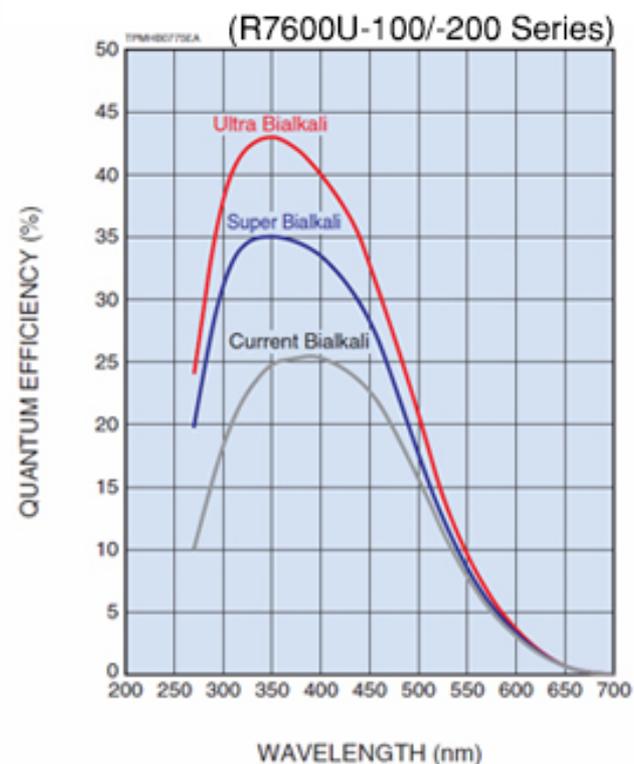


Photomultipliers and Photodetectors

- Photocathodes are used in photon detectors
 - Photomultiplier tubes for single photon counting
 - Photo tubes for pulse measurement
 - Streak cameras
- Tube manufacturers are a great source of information on cathode growth and performance



Typical Spectral Response Characteristics



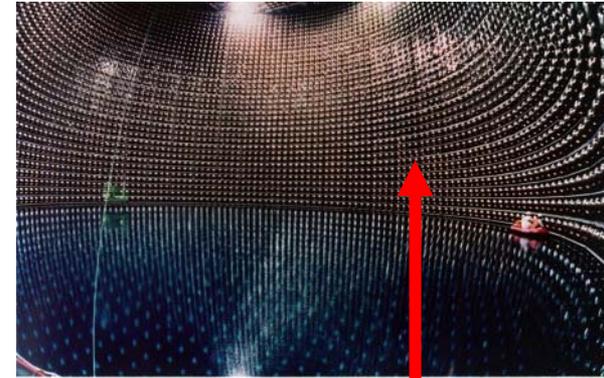
Learning from 60 Year History of Bialkali PMTs

K_2CsSb discovered by Sommer in 1950's

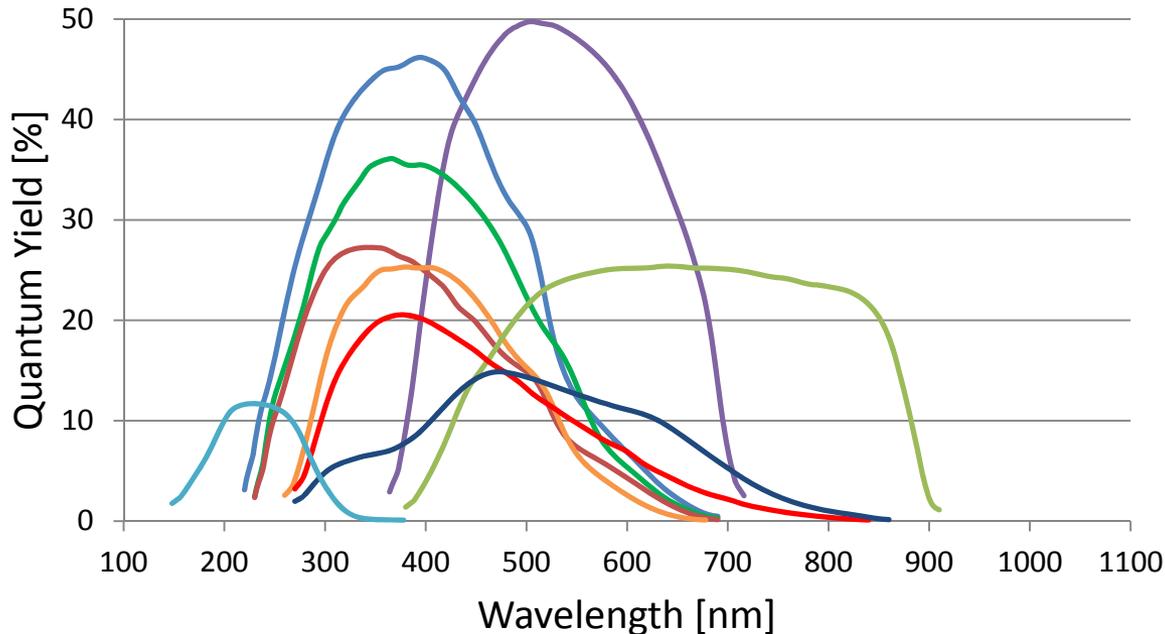
Bialkali PMTs:

Old peak QE $\sim 25\text{--}27\%$ (+40 years ago)

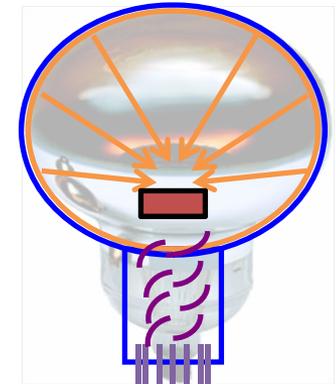
New peak QE $\sim 30\text{--}35\%$



Spectral Response of Commercial Photocathodes



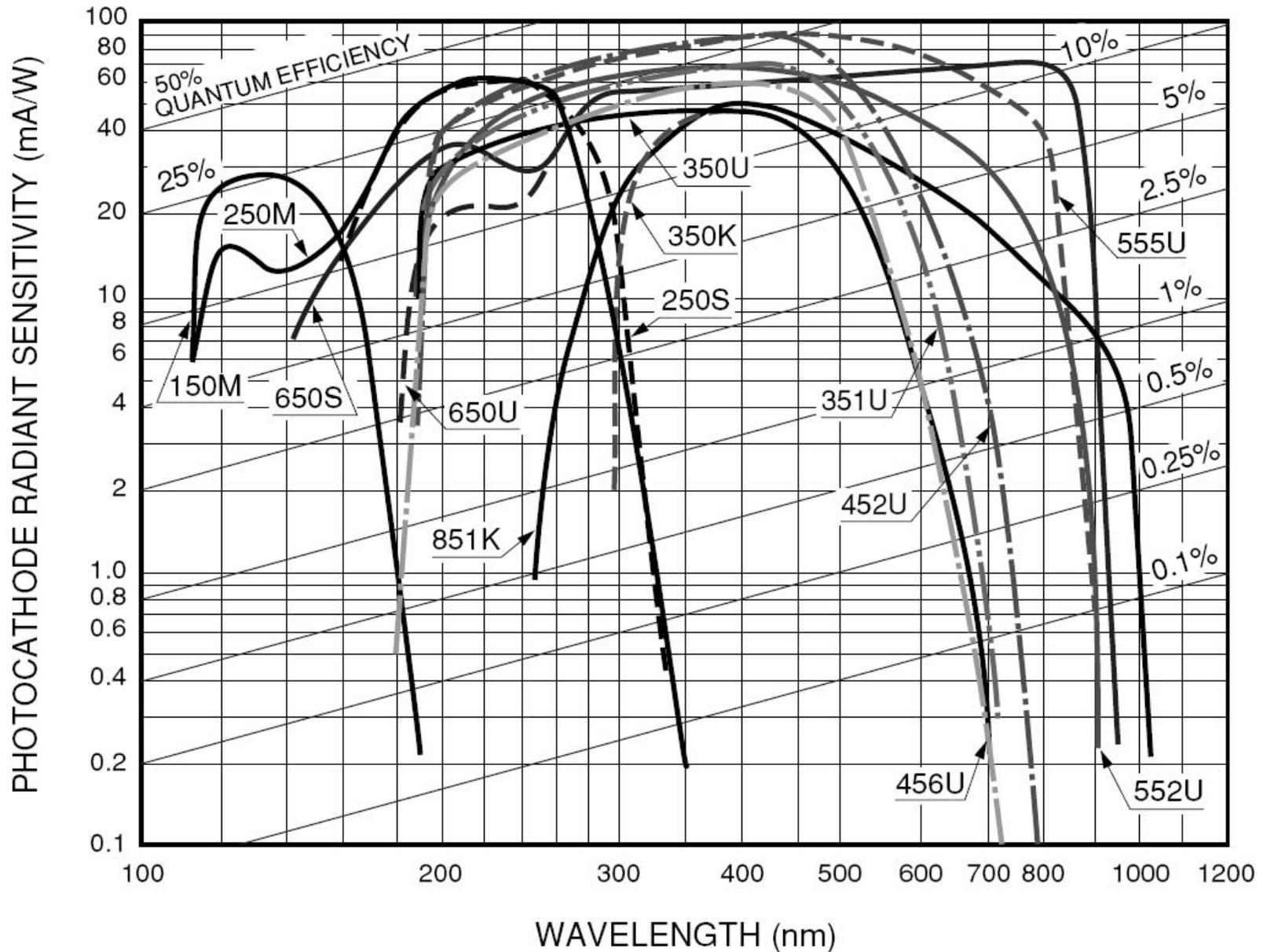
- GaAsP
- Ultra Bialkali
- Super Bialkali
- Conventional
- Bialkali
- GaAs
- Multialkali
- ERMA
- CsTe



Super-Kamiokande
Neutrino Detector
11,200 20"
 K_2CsSb PMTs

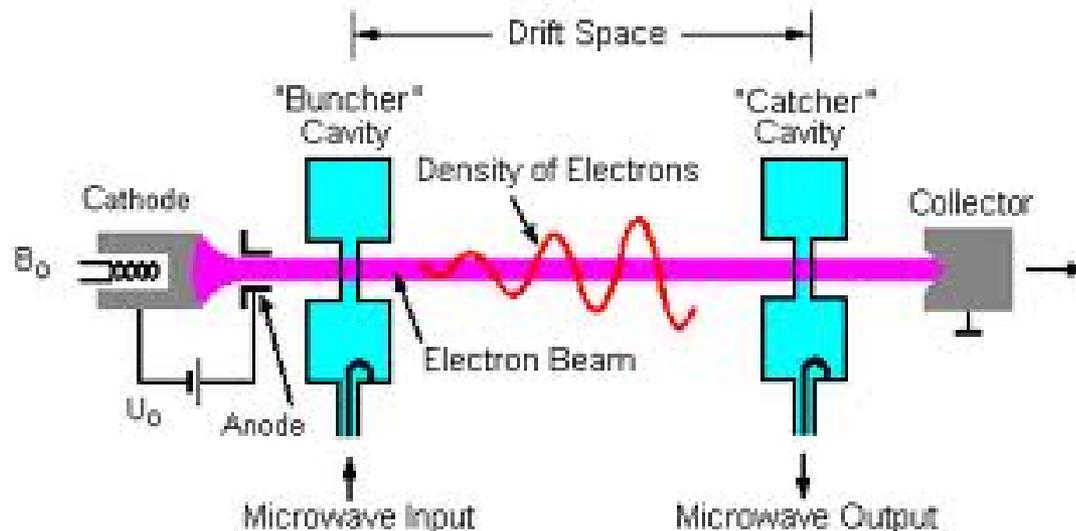
Hamamatsu Photocathodes

Reflection Mode Photocathodes



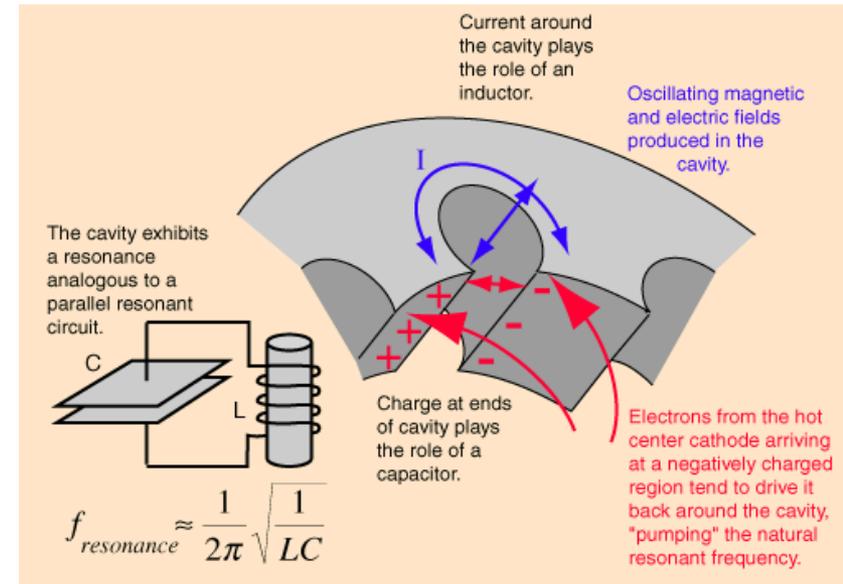
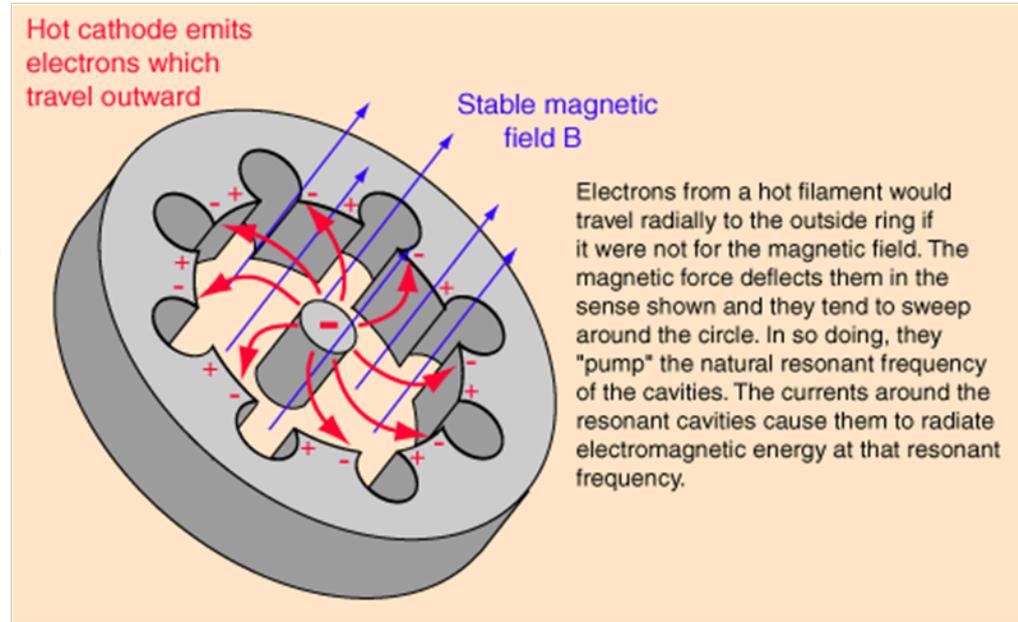
Klystrons — RF generators

- Klystrons use a DC electron beam at a few mA to generate/amplify microwaves by velocity modulation.
- Klystrons use thermionic cathodes to generate the required electron beam.



Magnetrons – RF generators

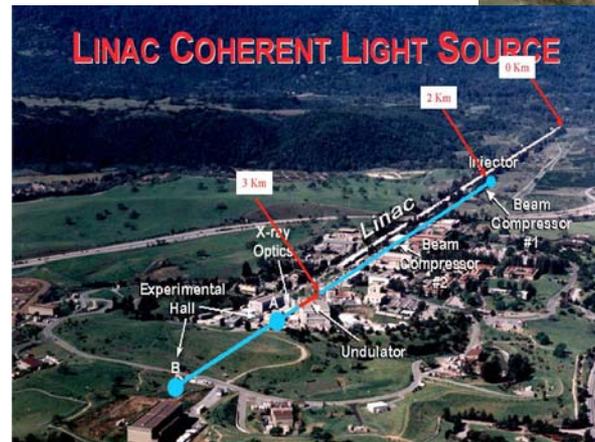
- Invented in 1921 and developed for radar during WWII
- Electrons from a thermionic cathode travel in a circle in presence of strong magnetic field
- Resonances excited in tubes that line the anode



Cathode Applications– Accelerators

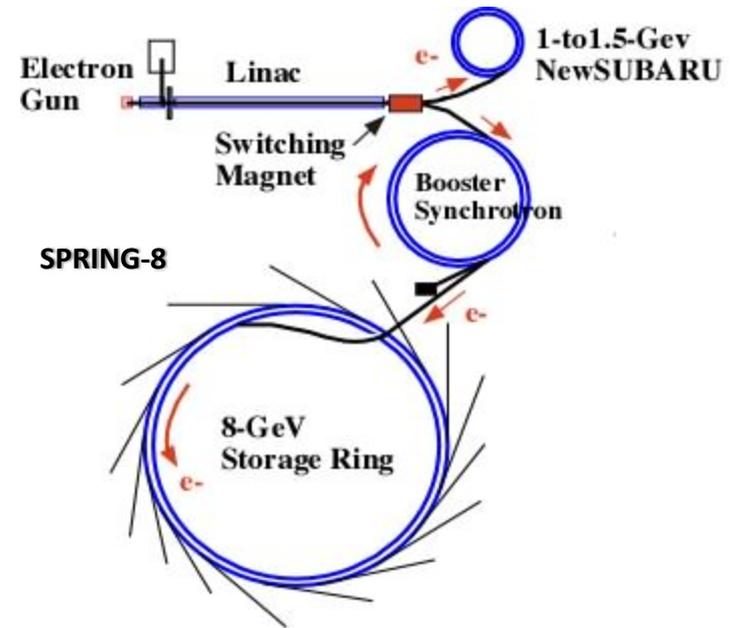
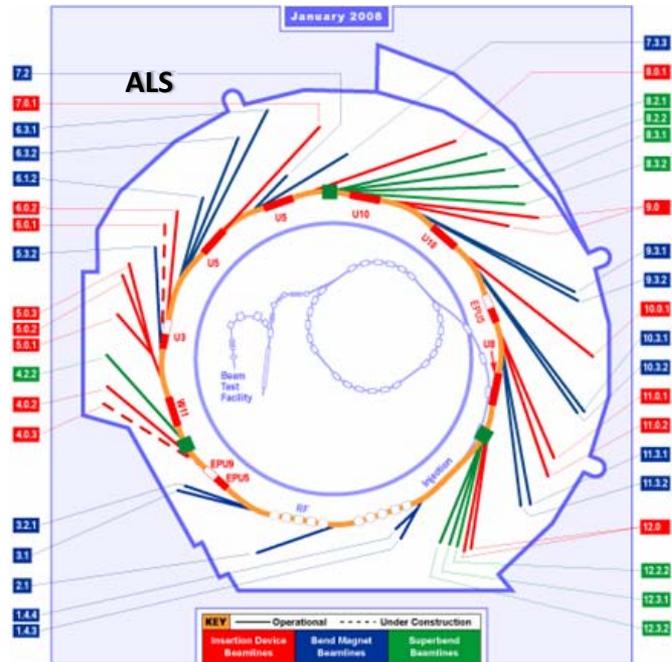
- Light sources typically use thermionic sources
 - Beam properties dominated by lattice, not cathode
 - This can be good and bad
- Electron machines for nuclear/particle physics (CEBAF, ILC, SLAC) typically require spin polarization and use special photocathodes
- Linacs (Flash, LCLS, ATF, Jlab FEL) typically use photocathodes – why?
- SCSS at Spring8 in Japan is a notable exception (*student topic?*)

National Synchrotron Light Source II



The Role of the Electron Injector in Light Sources

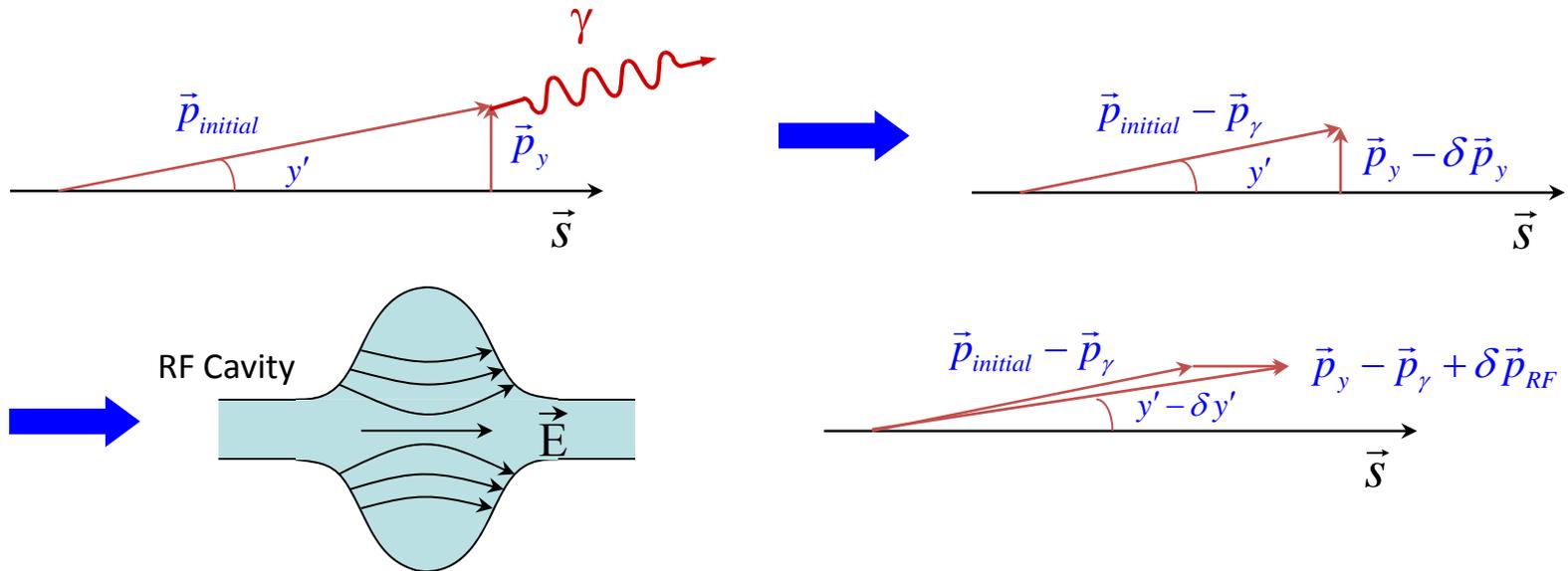
In 1st, 2nd and 3rd generation light sources, electron sources are part of the injector chain that typically includes a small linac and a “booster” ring. The beam generated by the electron gun goes through the linac and is then accelerated and stored in the booster for a time long enough that the 6D beam phase-space distribution is fully defined by the characteristics of the booster and not of the electron source.



Synchrotron Radiation and Radiation Damping

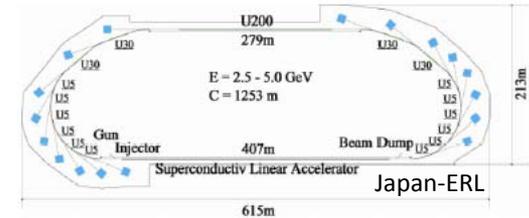
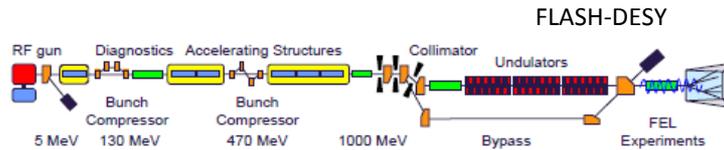
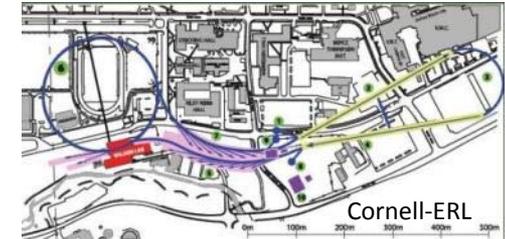
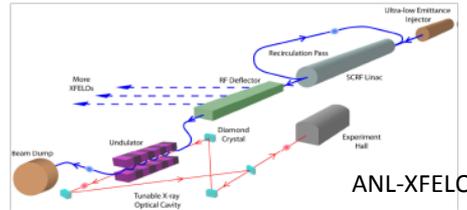
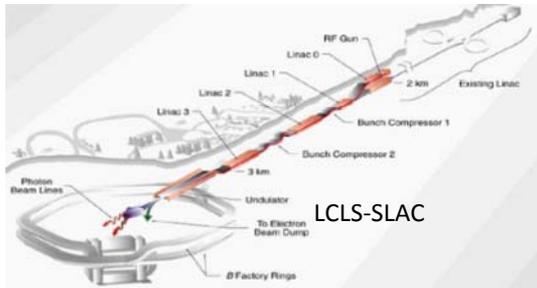
From Mark Palmer's Lecture at the 3rd ILC school

The energy lost by an electron beam on each revolution is replaced by radiofrequency (RF) accelerating cavities. Because the synchrotron radiation photons are emitted in a narrow cone (of half-angle $1/\gamma$) around the direction of motion of a relativistic electron while the RF cavities are designed to restore the energy by providing momentum kicks in the \hat{s} direction, this results in a gradual loss of energy in the transverse directions. This effect is known as radiation damping.



The Role of the Electron Injector in Light Sources

In linac based 4th generation light sources, such as free electron lasers (FELs) and energy recovery linacs (ERLs), the situation can be quite different. Indeed, in such a case, the final beam quality is set by the linac and ultimately by its injector and electron source.



In such facilities, the requirements for a large number of quasi-“monochromatic” electrons, concentrated in very short bunches, with small transverse size and divergence, translate into high particle density 6D phase-space, or in other words, in high **brightness** B :



$$B = \frac{N_e}{\epsilon_{nx} \epsilon_{ny} \epsilon_{nz}}$$

with N_e the number of electrons per bunch and $\epsilon_{nx, ny, nz}$ the normalized emittances for the planes $x, y,$ and z

The brightness generated at the electron source represents the ultimate value for such a quantity, and cannot be improved but only spoiled along the downstream accelerator

X-Ray 4th Generation Light Sources, the Most Challenging Electron Injector Case

- In FELs, the **matching condition for transverse emittance** drives towards **small normalized emittances**.



$$\varepsilon \approx \frac{\lambda}{4\pi} \Rightarrow \frac{\varepsilon_n}{\beta\gamma} \approx \frac{\lambda}{4\pi}$$

- The **minimum obtainable value for ε_n** defines the **energy of the beam** ($\gamma = E/mc^2$).

(with β the electron velocity in speed of light units, and assuming that an undulator with the proper period λ_u and undulator parameter K exist: $\lambda = \lambda_u / 2\gamma^2(1 + K^2/2)$)

- We will see later, that for the present electron gun technologies:
 $\varepsilon_n < \sim 1 \mu\text{m}$ for the typical $< \sim 1 \text{ nC}$ charge/bunch.

For X-Ray machines ($\lambda < \sim 1 \text{ nm}$) that implies GeV-class electron beam energy, presently obtainable by long and expensive linacs.

- Similar transverse emittance requirements apply also to ERLs.

- In X-Ray FELs the matching condition for the energy spread requires a fairly **low energy spread** as well



$$\frac{\sigma_E}{E} < \sim \rho_{Pierce} < \sim 10^{-3}$$

- Achieving the necessary FEL gain requires high peak current ($\sim 1 \text{ kA}$), and **hence high charge/bunch and short bunches**.
- In both ERLs and FELs, high-time resolution user-experiments require extremely short X-Ray pulses (down to sub-fs) imposing the need for **small and linear longitudinal emittances** to allow for the proper compression along the linac.

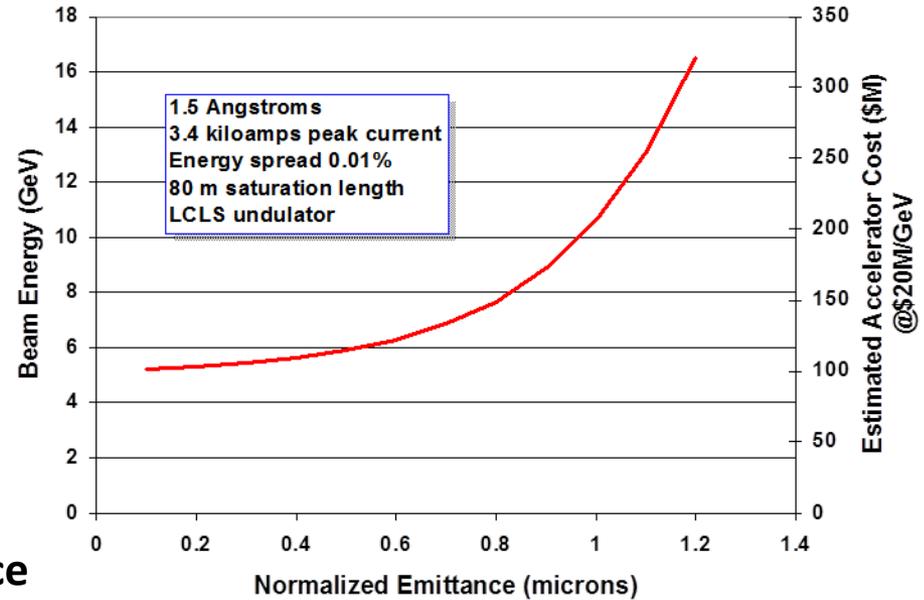
In summary, 4th generation X-Ray facilities challenge the performance of electron injectors.

Motivation for Brighter Electron Beams

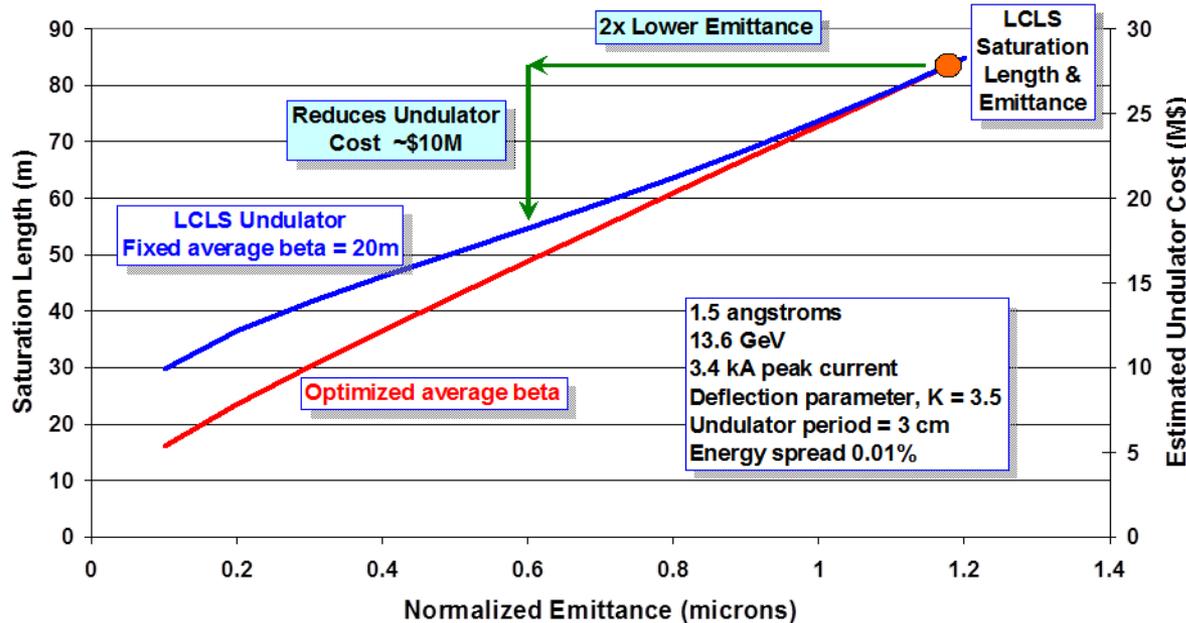
High energy electron beams are expensive

A poor beam can still laser at a high enough energy:

$$\frac{\epsilon N}{\gamma} < \frac{\lambda_{FEL}}{4\pi}$$



Gain length and undulator cost vs. emittance



A poor beam increases the gain length which in turn increases to the undulator cost

*Doesn't include cost of infrastructure

The (obviously) most important Photocathode properties

•Quantum efficiency

- High QE at the longest possible wavelength
- Fast response time: <100 ps
- Uniform emission
 - Non-uniform emission seeds emittance growth due to transverse, space charge expansion
- Easy to fabricate, reliable, reproducible
- Low dark current, field emission.

•Intrinsic emittance

- Low as possible
 - Atomically flat: ~few nm p-p, to minimize emittance growth due to surface roughness and space charge
- Tunable, controllable with photon wavelength
 - May need to “chase” the work function: $\varepsilon_{\text{intrinsic}} \propto \sqrt{\hbar\omega - \phi_{\text{eff}}}$
- Better at cryogenic temperatures?

•Lifetime, survivability, robustness, operational properties

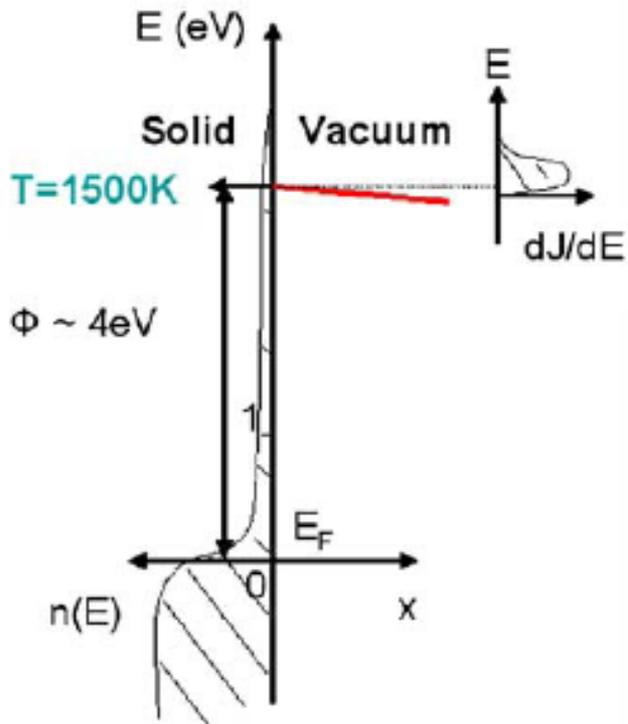
- Require >1 year of operating lifetime
 - reasonable vacuum level: 10^{-10} Torr range
- Easy, reliable cathode cleaning or rejuvenation or re-activation
- Low field emission at high electric fields
 - needs to be atomically flat: ~few nm p-p
- Reliable installation and replacement system (load lock)

Overview

- Thermionic Cathodes
- Field Emitters
 - Field Emitter Arrays
 - Needle Cathodes
- Photocathodes
 - Metallic Photocathodes
 - Normal Conductors
 - Superconductors
 - Semiconductor Photocathodes
 - Positive Electron Affinity
 - Alkali Antimonides
 - Cesium Telluride
 - Negative Electron Affinity (Cs: GaAs)
- Photo-field emission
- Diamond Electron Amplifier

Emission Options

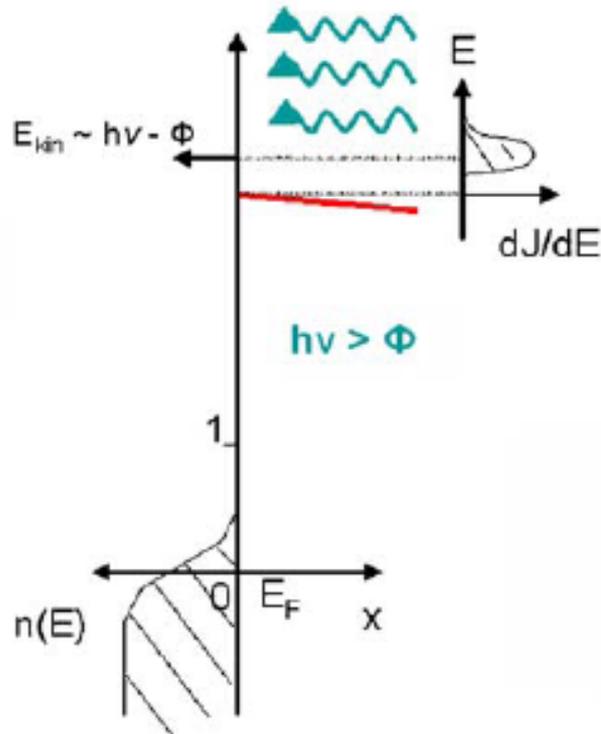
Thermionic Emission



$$E_{kin} \sim \frac{3}{2} kT_{Solid}$$

$$J < 10^6 \text{ A.m}^{-2}$$

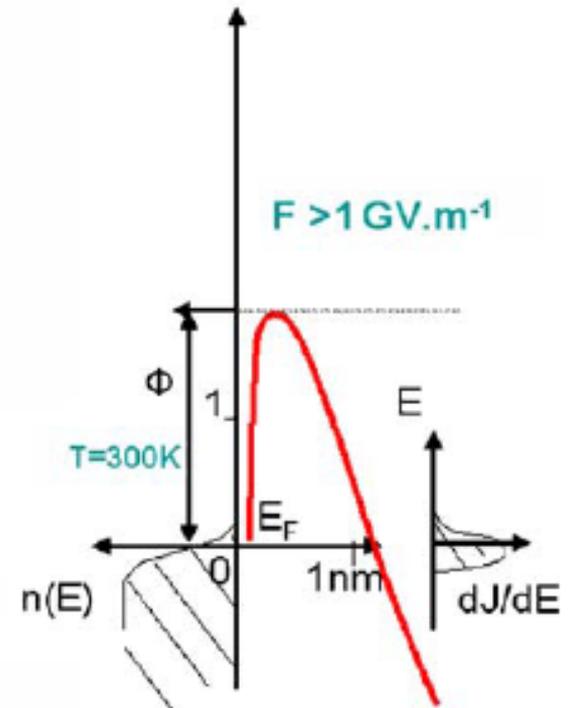
Photoemission



$$E_{kin} \sim h\nu - \Phi + e \sqrt{\frac{eF}{4\pi\epsilon_0}}$$

$$J < 10^9 \text{ A.m}^{-2}$$

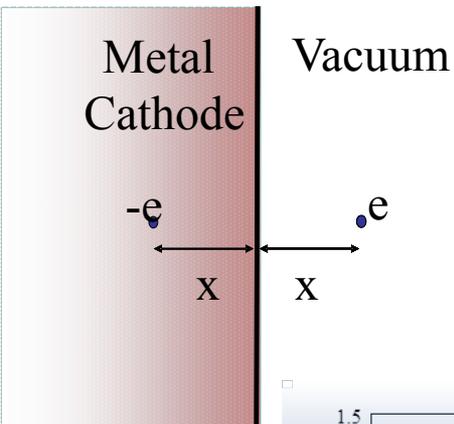
Field Emission



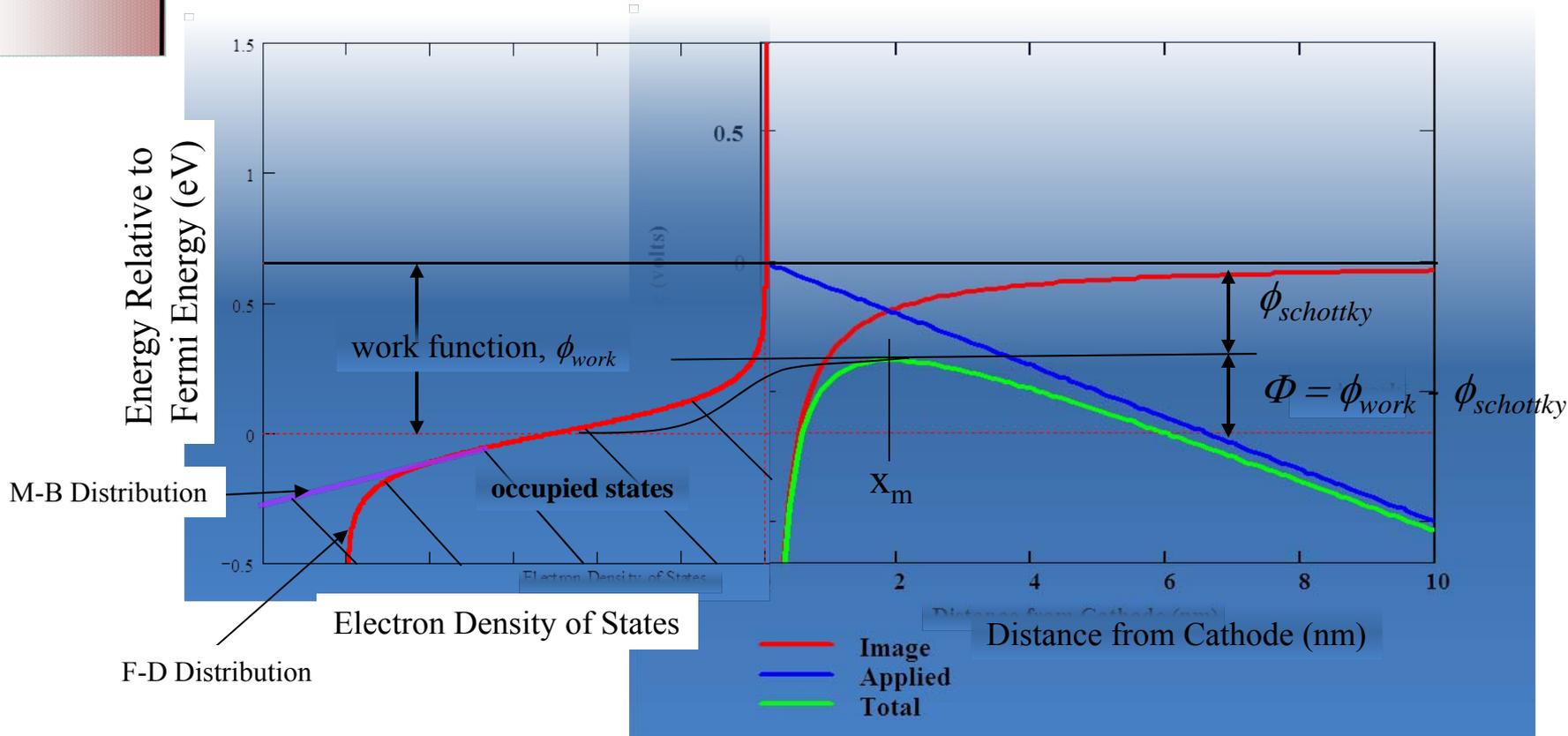
$$E_{kin} \sim 4kT_{Solid}$$

$$J < 10^{12} \text{ A.m}^{-2}$$

Emission Barrier and Schottky effect



$$e\Phi = e\phi_{work} - \frac{e^2}{16\pi\epsilon_0 x} - eE_0x$$



Thermionic and Field Emitters

Good for true DC and long pulse duration applications

The good points:

- Low transverse emittance
- Simple
- Tolerant of poor vacuum
- Long lifetime (10^4 hrs)

However:

- Long bunches (100 ps+)
- Large longitudinal emittance
- Lack of control of profile
- Complicate Linac (Bunchers, Compressors)

Types:

Thermionic (LaB_6 , CeB_6 , Scandate, BaO)

Field Emitter Arrays (Spindt Cathode)

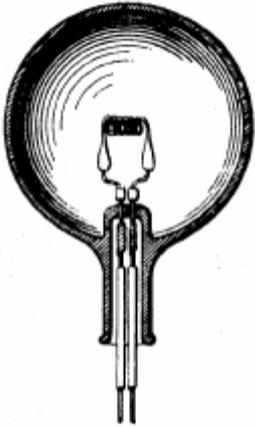
Needle Cathode

Photo-Assisted Field emission

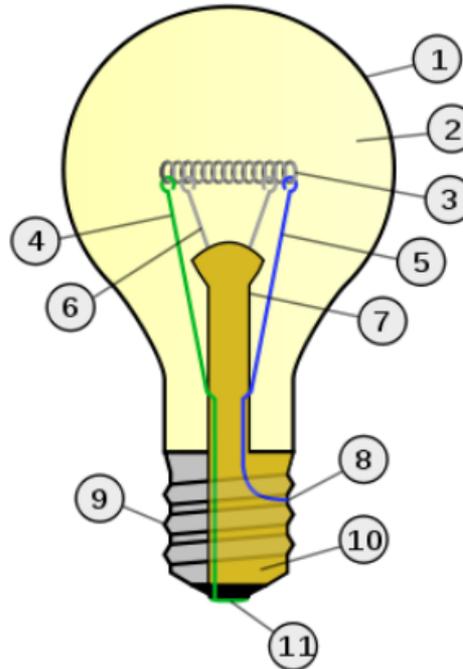
Thermionic Emission

Used to make light....

- Studied since early 1800's and perfected over 100 years, by many inventors (why does Edison get so much credit?)
- Thermionic emission from Tungsten filaments and metalloids like LaB6 operating at $>1000\text{K}$ are common
- $> 90\%$ of consumed power simply generates heat
- Often low vapor pressure filaments are used, to avoid coating tubes

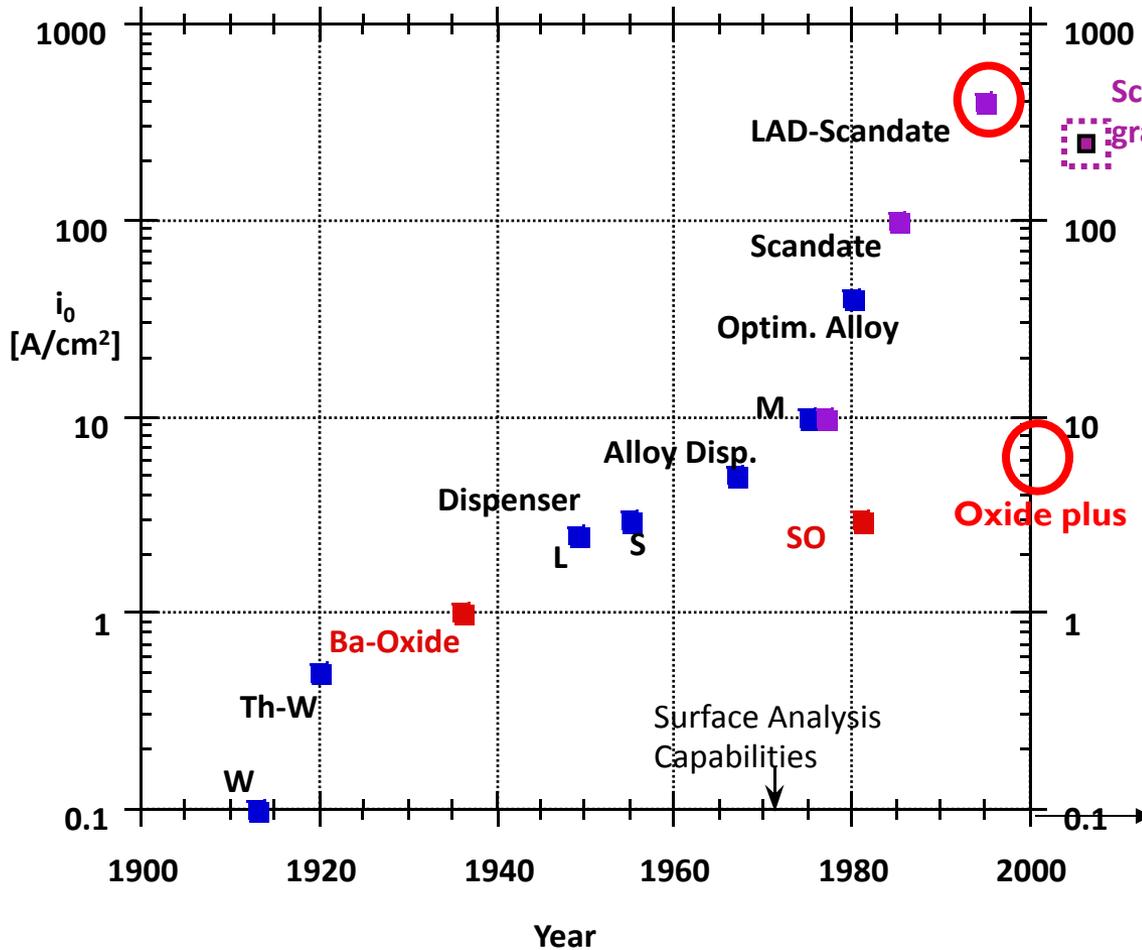


Edison's patent,
Long-lasting filament



1. Outline of Glass bulb
2. Low pressure inert gas (argon, neon, nitrogen)
3. Tungsten filament
4. Contact wire (goes out of stem)
5. Contact wire (goes into stem)
6. Support wires
7. Stem (glass mount)
8. Contact wire (goes out of stem)
9. Cap (sleeve)
10. Insulation ([vitrite](#))
11. Electrical contact

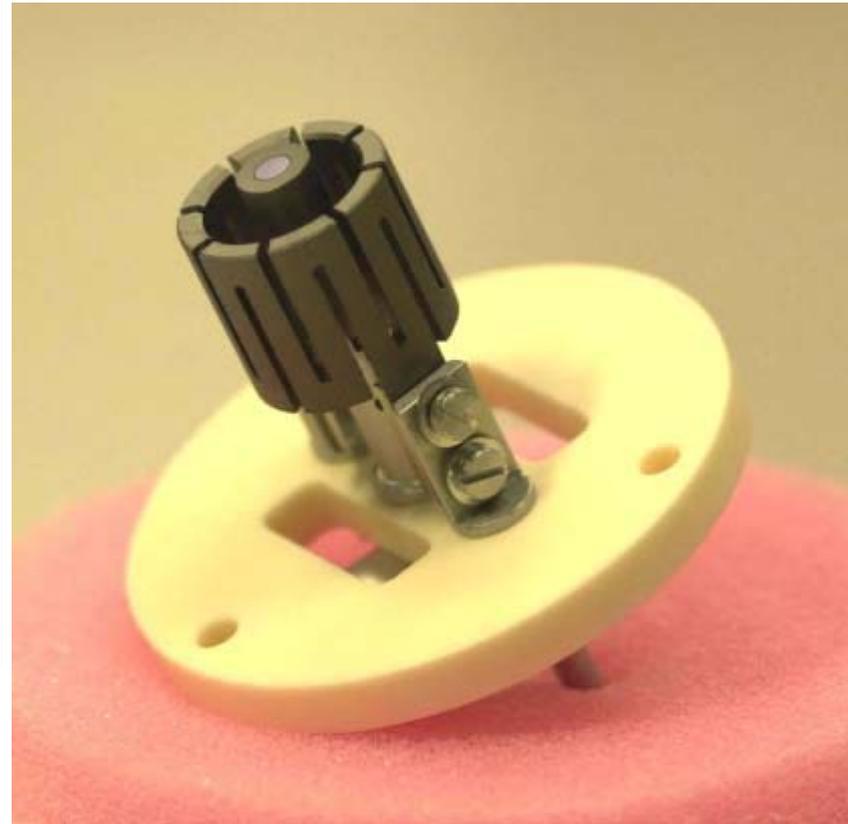
Vacuum electron sources



Historical development of thermionic cathode emission capabilities (life $t_{op} \geq 4000$ h at saturated emission current density i_0).

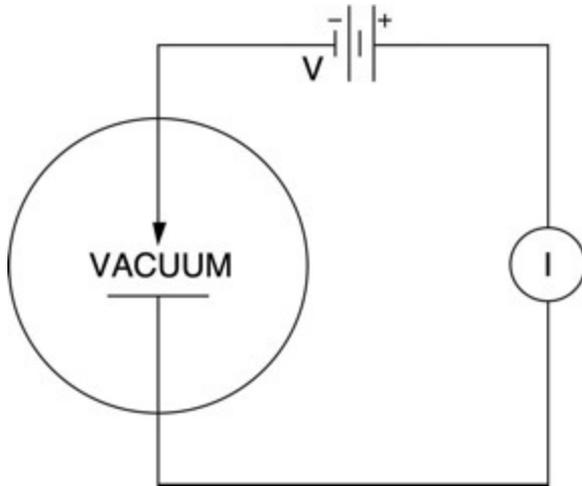
Spring8 CeB₆ Cathode for XFEL (SCSS)

| | |
|--|-----------------------|
| Beam Energy | 500 keV |
| Peak Current | 1~3A |
| Pulse Width (FWHM) | 2 μ sec |
| Repetition Rate | 60 Hz |
| Cathode Temperature | 1400~1600 deg.C |
| Cathode Diameter | 3mm |
| Theoretical Thermal Emittance (rms) | 0.4 μ mm.mrad |
| Measured Normalized Emittance (rms, 90% particles) | 0.6 μ mm.mrad [7] |



Chopper, Pre-buncher and Bunch compressor used to reduce pulse to 0.7 ps

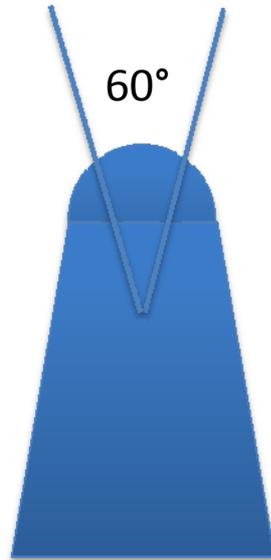
Field Emitter Sources



$$I = BV^2 \exp(-C/V)$$

Vacuum diode

- Explained by Fowler-Nordheim, 1928: a quantum mechanical tunneling effect
- “bright” e-beam, good for surface science

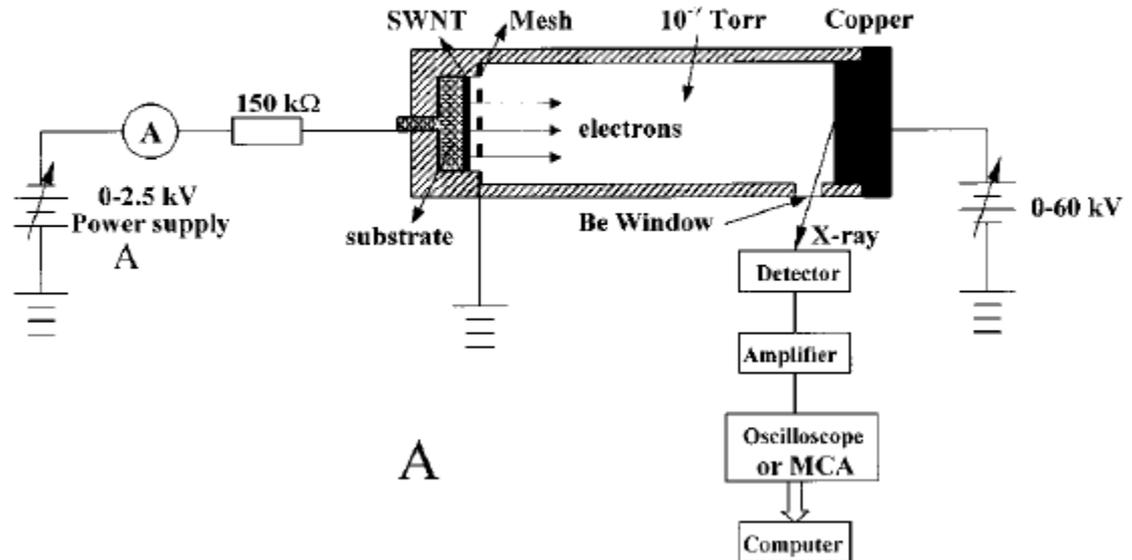
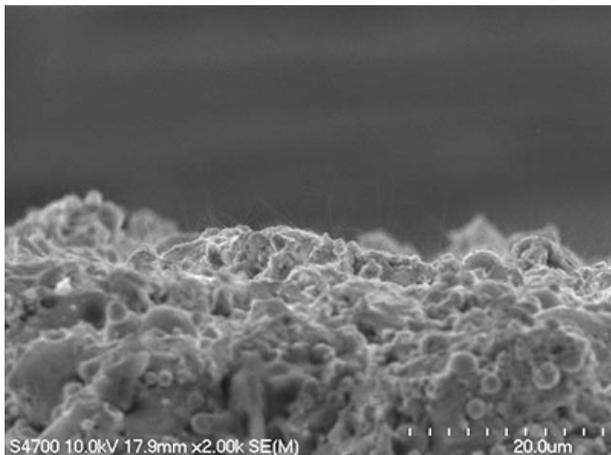


$$I \approx A \times 1.54 \times 10^{-6} \frac{F^2}{\phi} \exp \left[-6.83 \times 10^9 \frac{\phi^{3/2}}{F} \right]$$

Carbon Nanotube FE source

Yue et al.

- Single wall carbon nanotubes



APPLIED PHYSICS LETTERS

VOLUME 81, NUMBER 2

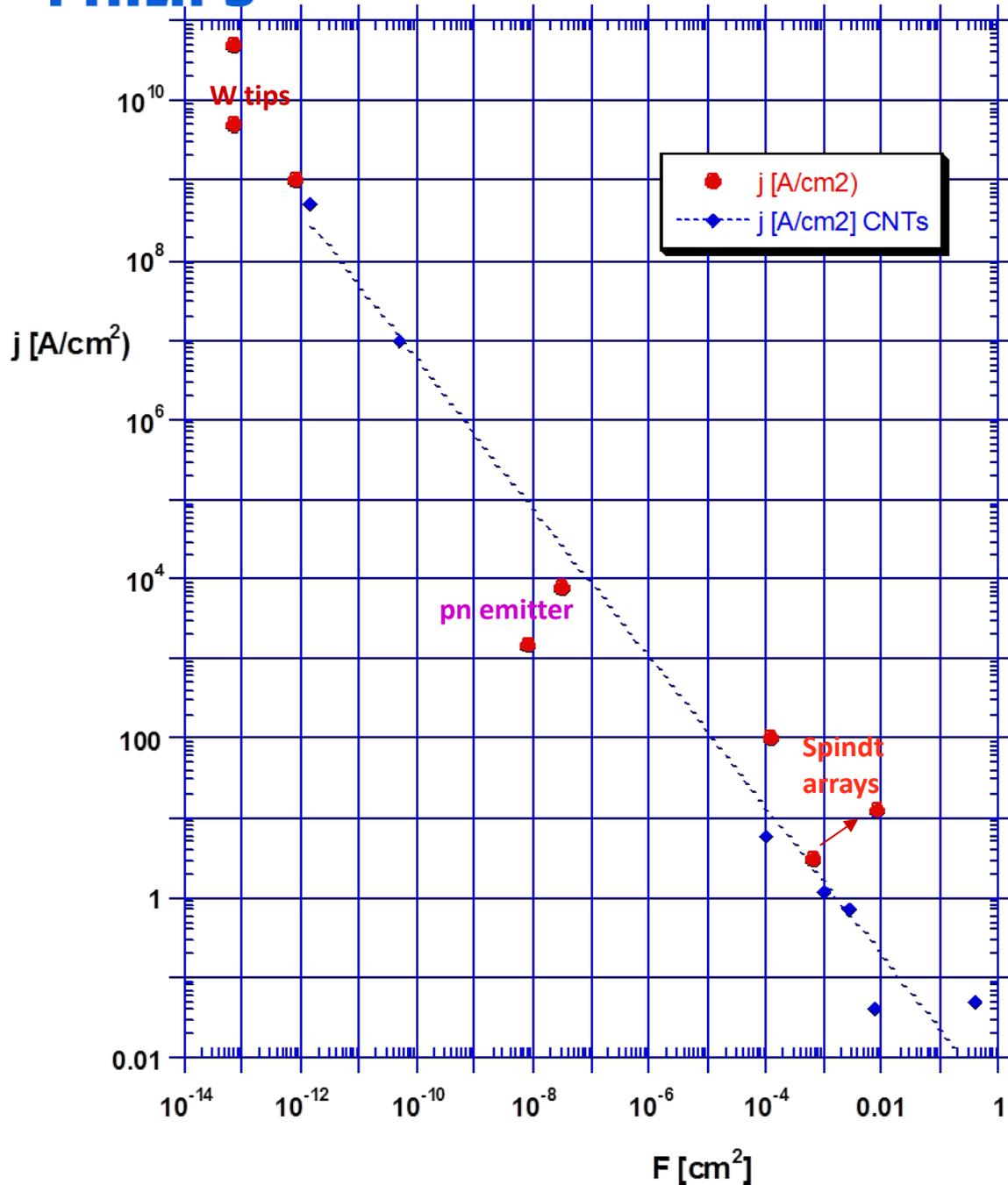
8 JULY 2002

Generation of continuous and pulsed diagnostic imaging x-ray radiation using a carbon-nanotube-based field-emission cathode

G. Z. Yue

Department of Physics, University of North Carolina, Chapel Hill, North Carolina 27599





**Field emission (cold emission)
current density versus emitter area
(including passive parts)**

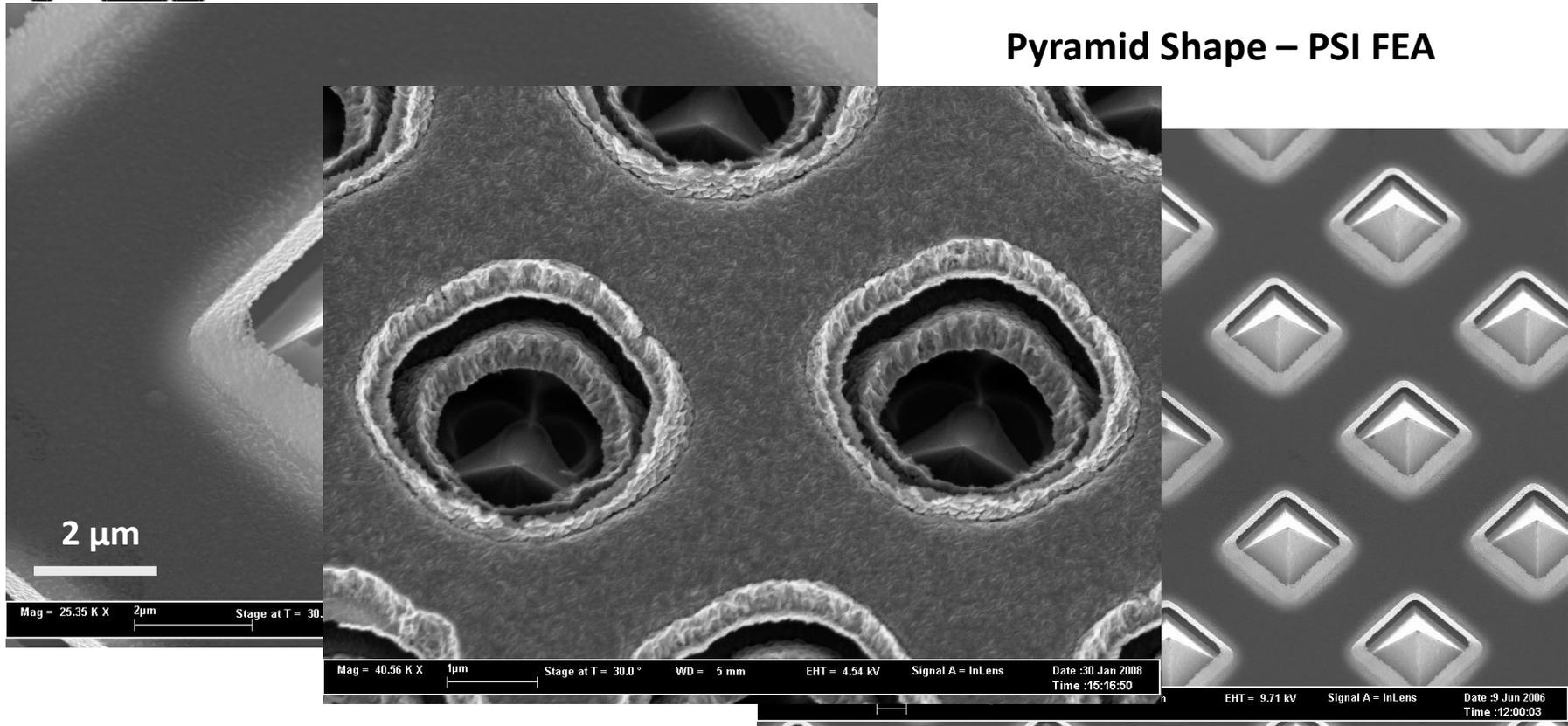
**In order to judge an improvement of FE / cold emitters over time
a good comparison can only be made
for a fixed emitting area;
Also the increase of the total area
can be seen as improvement**

**The blue symbols are CNT emitters. The
fitted curve is a power law
 $j = 0.00246 * (F/\text{cm}^2)^{-0.935}$ [A /cm²]**

**Limiting effects:
non-emitting parts/ gate, field
shielding, space charge, thermal load**

Slide courtesy of G. Gaertner, Philips

PSI Field Emitter Array



Source: S. Tsujino; E. Kirk

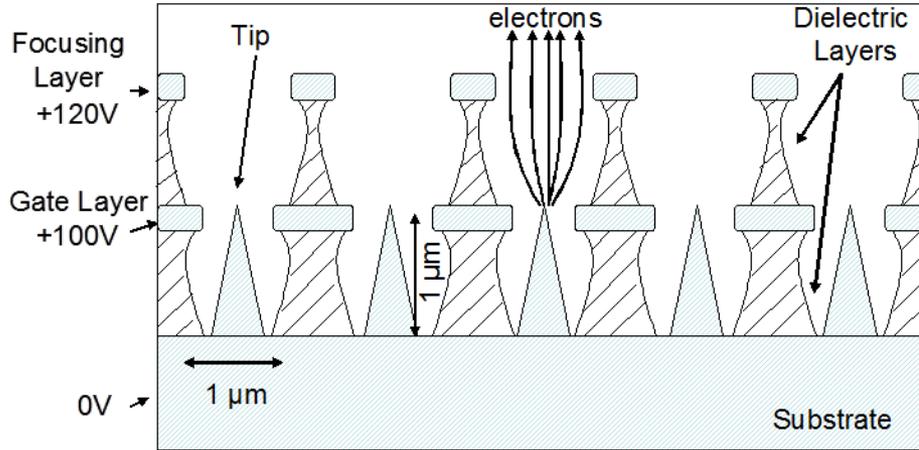
- Mo Tips (Field Enhancement Factor: $\langle \beta \rangle \sim 90$)
- Metallic wafer; Molding Technique
- $10\mu\text{A}$ per tip DC (gate bias $\sim 200\text{V}$)

April 2008 PSI: First Double Gated – All Metal FEA

S. C. Leemann, A. Streun, A. F. Wrulich, Phys. Rev. ST Accel. Beams 10, 071302 (2007)
 A. Oppelt *et al.*, FEL07, 224

Slide courtesy of R. Ganter, PSI

Double Gated FEA



$$\epsilon_{n,rms} (1^{st} \text{ Gate}) \sim \beta\gamma \cdot n \cdot \delta x \cdot \vartheta$$

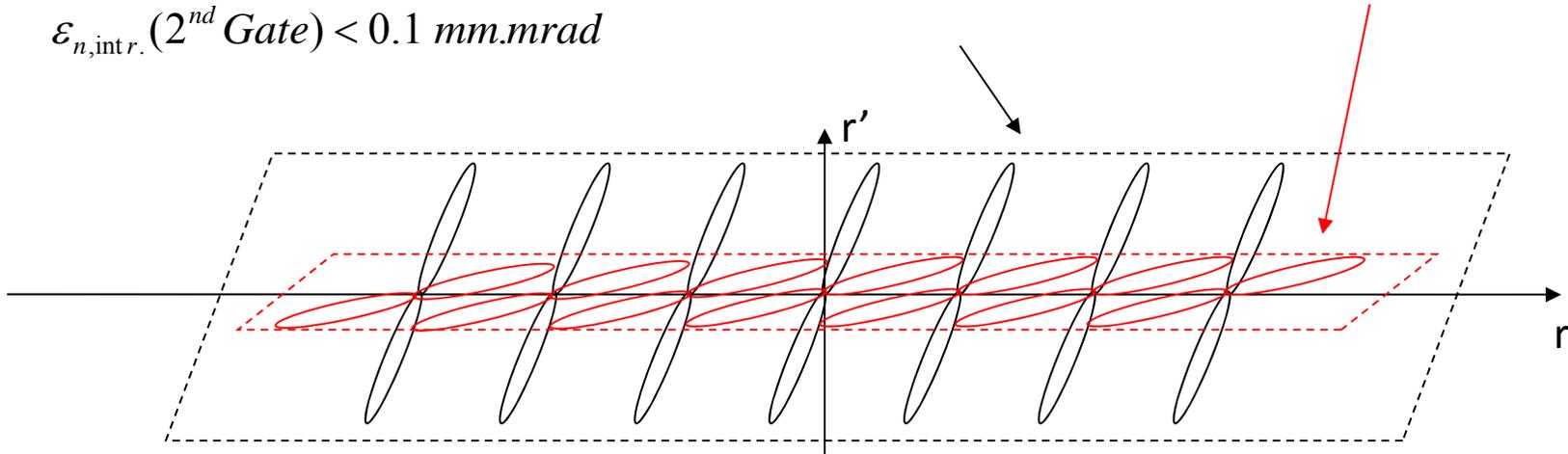
$$\beta\gamma \cdot \vartheta = 5 \text{ mrad} \quad n=100; \delta x=2\mu\text{m}$$

$$\epsilon_{n,rms} (1^{st} \text{ Gate}) \sim 2 \text{ mm.mrad}$$

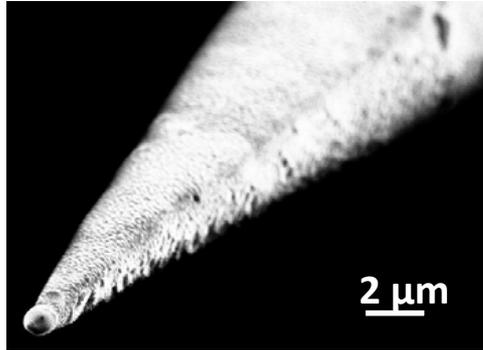
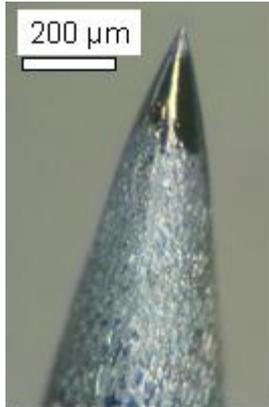
$$\epsilon_{n,int r.} (2^{nd} \text{ Gate}) < 0.1 \text{ mm.mrad}$$

Initially
 $\epsilon_n \sim 2 \text{ mm.mrad}$

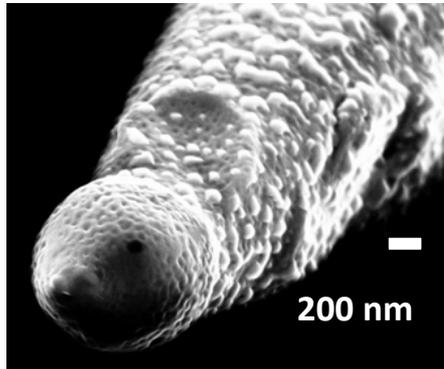
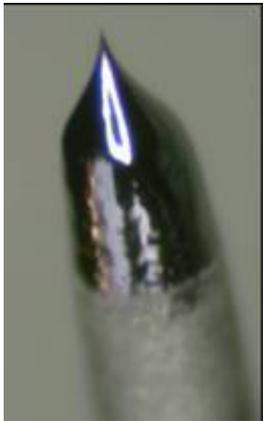
After Focusing
 $\epsilon_n < 0.1 \text{ mm.mrad}$



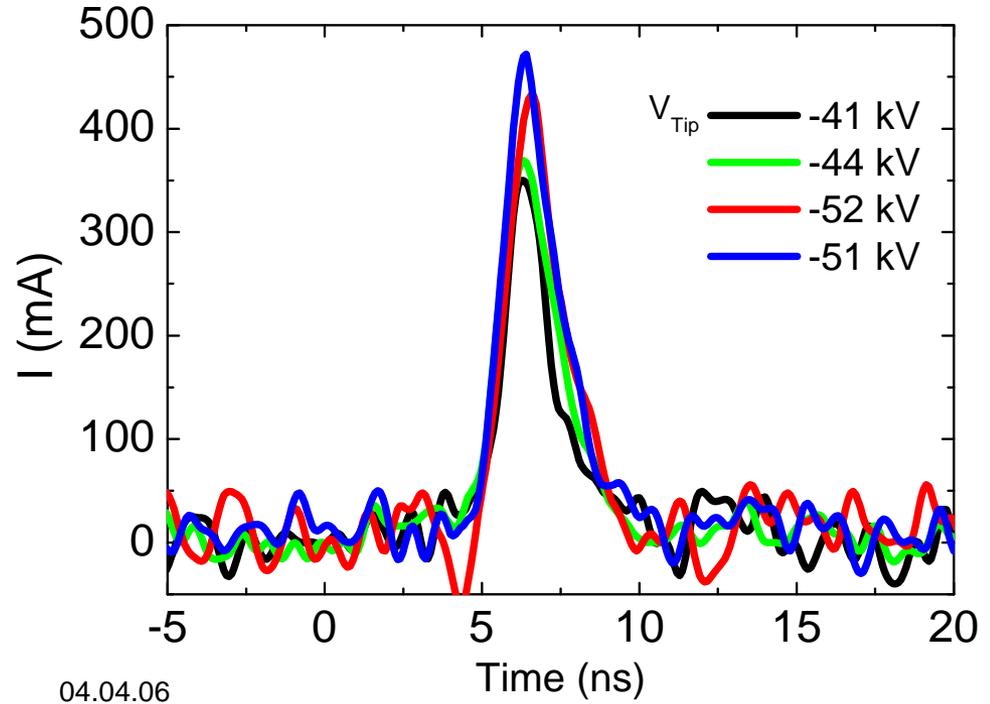
Needle Cathode



$r_{\text{apex}} \sim 1 \text{ to } 5 \mu\text{m}$



ZrC Single Crystal (100):
robust, $\Phi_{\text{ZrC}} \sim 3.5 \text{ eV}$



Peak Current
in Field Emission mode
 $\sim 500 \text{ mA}$

Commercial Devices from A. P. Tech Inc.

Photoinjector Basics

Why use a Photoinjector?

Electron beam properties
determined by laser

- Timing and repetition rate
- Spatial Profile
- Bunch length and temporal profile (Sub-ps bunches are possible)

High peak current density
 10^5 A/cm²

Low emittance/temperature
<0.2 μ m-rad

Useful relation:

$$hc = 1239.8[eV \cdot nm] = \lambda \cdot E$$

Cathode/Injector Properties

Quantum Efficiency (QE)

$$QE = \frac{\#e^-_{emitted}}{\#\gamma_{incident}} = h\nu \frac{I}{P}$$

Lifetime: time (or charge) required
for QE to drop to 1/e of initial

Response Time: time required for
excited electrons to escape

Emittance: Correlation between
the position and momentum of
particles in the bunch

Peak Current: $I_p = \frac{Q_{bunch}}{\tau_{bunch}}$

The Old Standby - Metals

Normal conducting RF photoinjectors often use metal cathodes, either Cu (simplicity) or Mg (higher QE)

The good points:

- Basically unlimited lifetime (with occasional laser or ion cleaning)
- Tolerant of poor (nTorr) vacuum
- Prompt response time (fs)
- Low field emission

However

- Require UV laser
 - Typical QE of 10^{-5} to 10^{-3}
- } Not suitable for >1 mA injectors

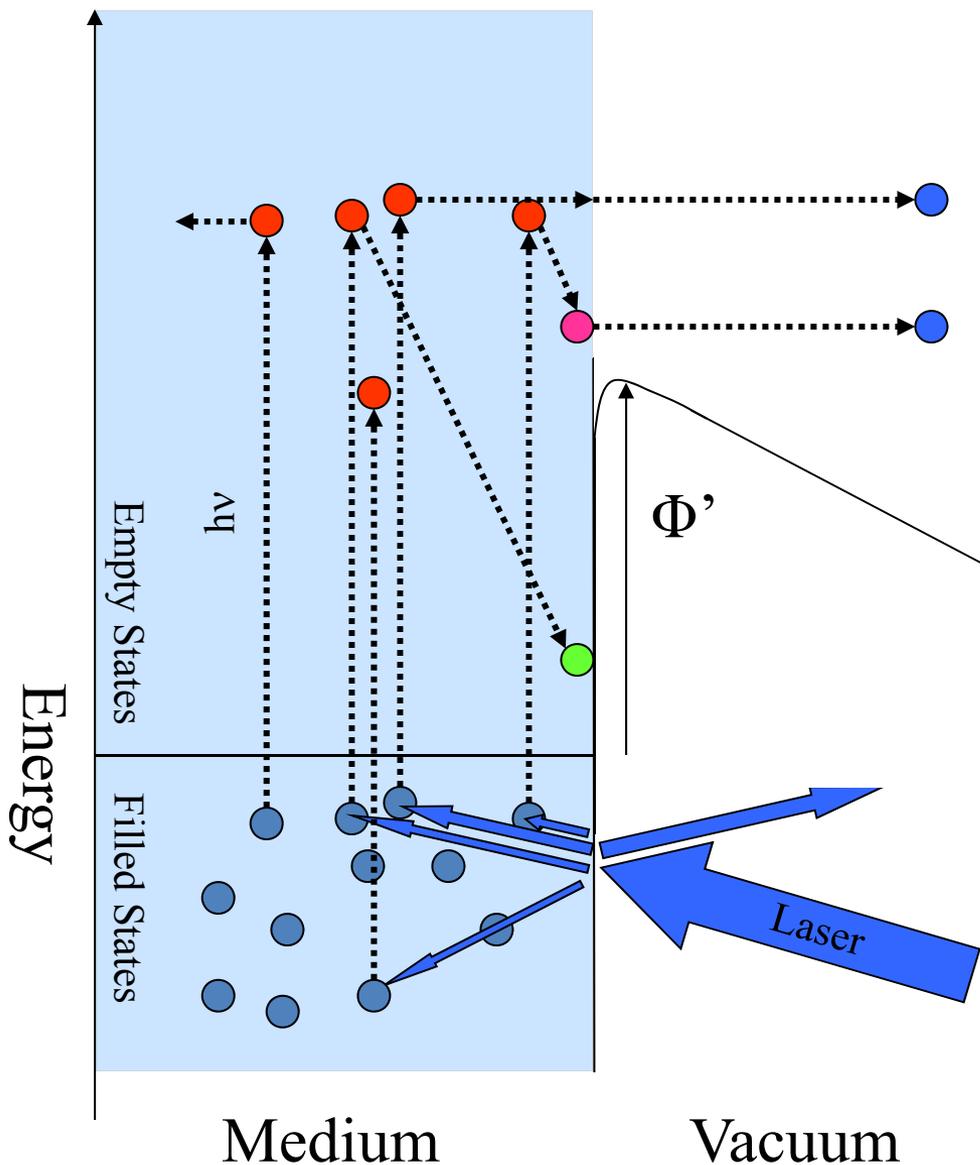
Magnesium QE @ 266 nm = 0.2% @ 266nm

W.F. Krolikowski and W.E. Spicer, Phys. Rev. 185, 882 (1969)

D. H. Dowell *et al.*, Phys. Rev. ST Accel. Beams 9, 063502 (2006)

T. Srinivasan-Rao *et al.*, PAC97, 2790

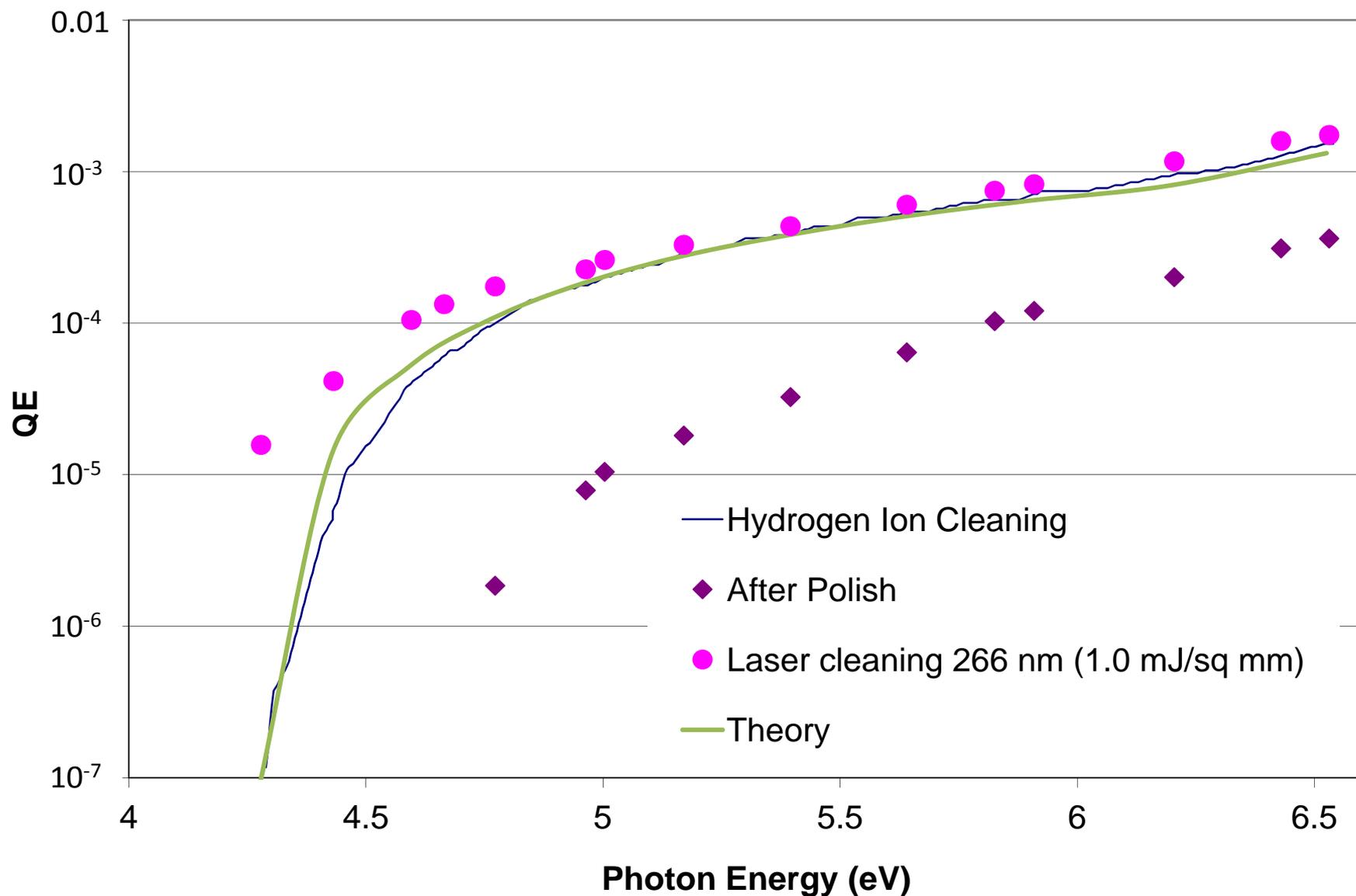
Three Step Model of Photoemission - Metals

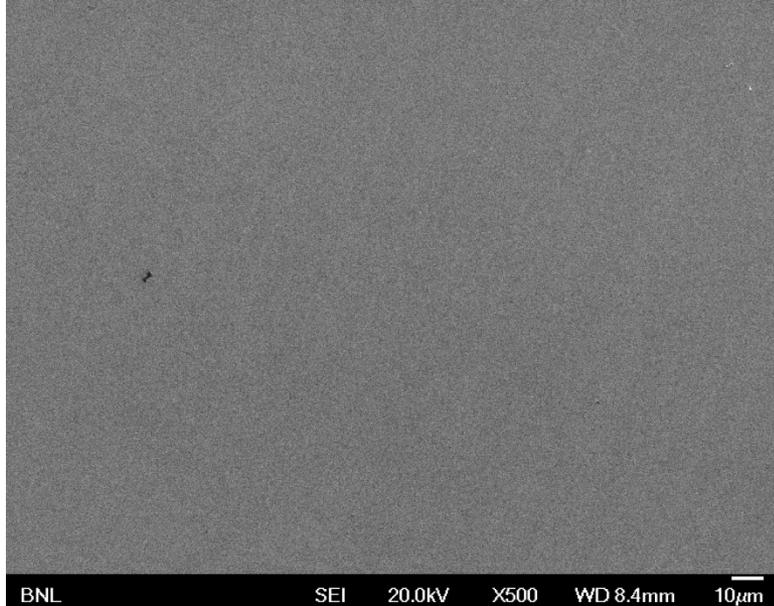


- 1) Excitation of e^- in metal
Reflection
Absorption of light
Energy distribution of excited e^-
- 2) Transit to the Surface
 e^-e^- scattering
mfp ~ 50 angstroms
Direction of travel
- 3) Escape surface
Overcome Workfunction
Reduction of Φ due to applied field (Schottky Effect)

Integrate product of probabilities over all electron energies capable of escape to obtain Quantum Efficiency

LCLS Copper Cathodes

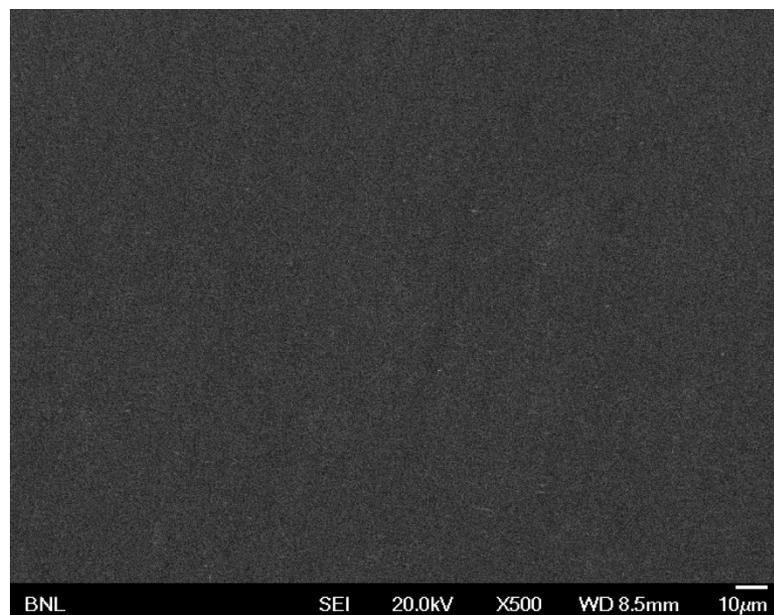




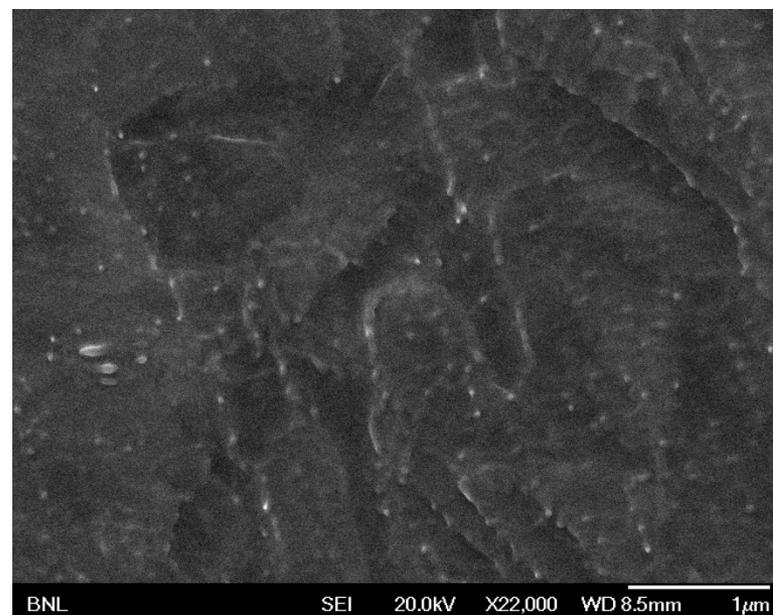
Before, x500



Before, x20k



After, x500



After, x20k

Superconducting Photocathodes

The cathode-cavity interface is the most difficult part a superconducting injector

Using a superconductor as a cathode removes the need for a RF choke, and may allow higher gradients

Niobium is a poor photocathode -> use Lead

Two $\frac{1}{2}$ cell cavities (1.3 & 1.42 GHz) have been tested

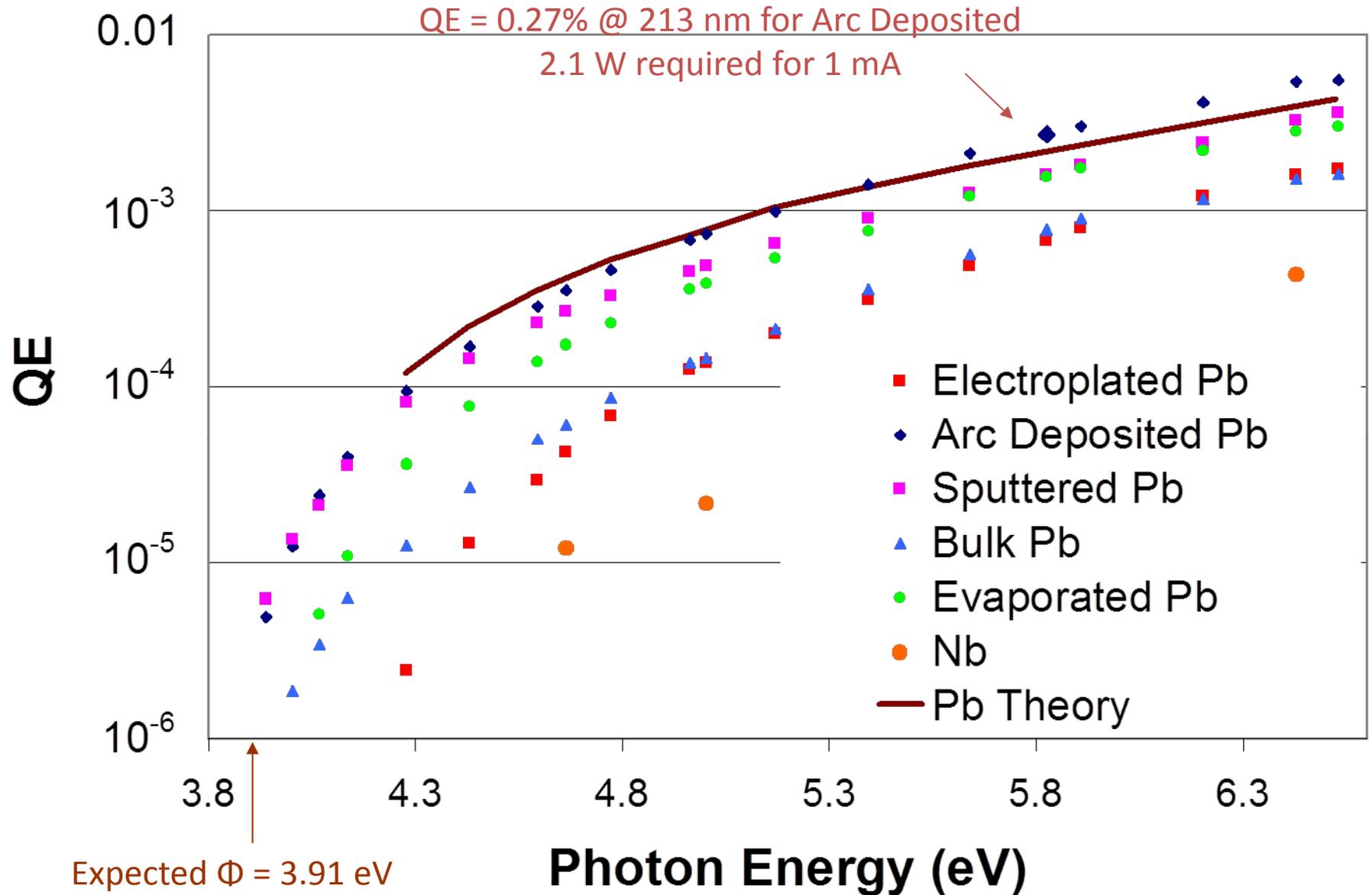
- Both reached 40 MV/m; RF performance unaffected by lead
- Lead cathode QE comparable to room temperature values
- Peak laser power of 3 MW/cm² (@ 248 nm) did not quench the cavity

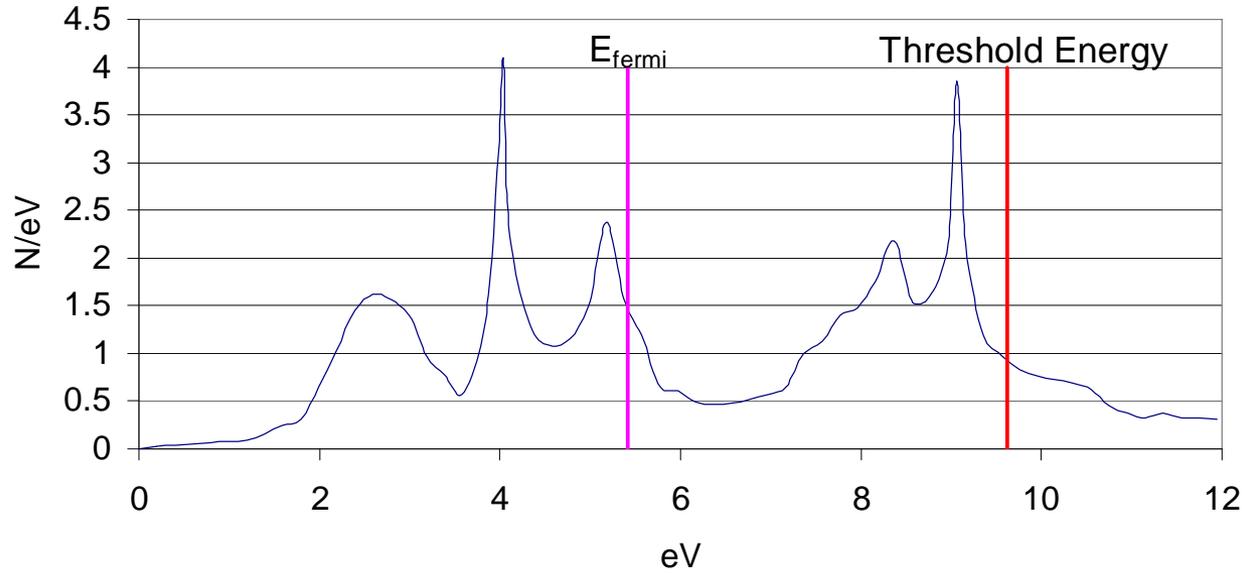
J. Smedley, T. Rao, and Q. Zhao, J. Applied Physics 98, 043111 (2005)

J. Smedley, T. Rao, J. Sekutowicz, Phys. Rev. ST Accel. Beams 11, 013502 (2008)

J. Smedley *et al.*, PAC07, 1365; J. Sekutowicz *et al.*, PAC07, 962

DC Room Temperature Photoemission Results





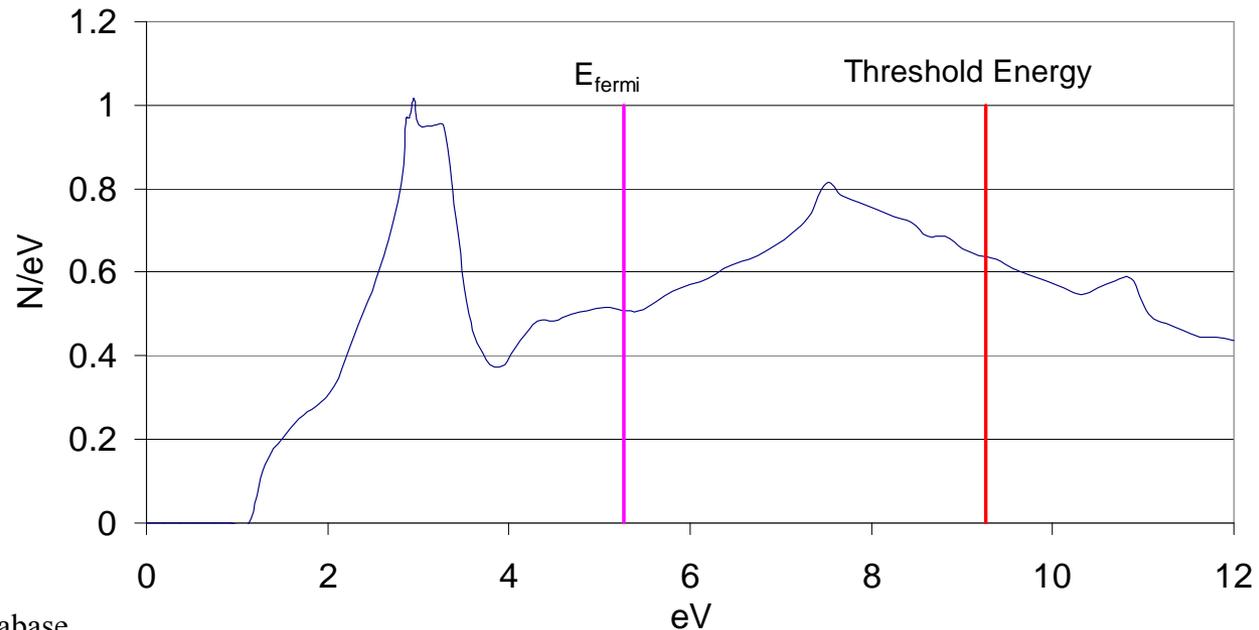
Density of States for Nb

Large number of empty conduction band states promotes unproductive absorption

Density of States for Lead

Lack of states below 1 eV limits unproductive absorption at higher photon energies

Lead Density of States



Semiconductor Photocathodes

The primary path to high average current in photoinjectors

The good points:

- QE can be >10%
- Many use visible light
- Polarized cathodes possible

However:

- Require UHV (<0.1 nTorr)
- Limited Lifetime
- Response time
- Complicated

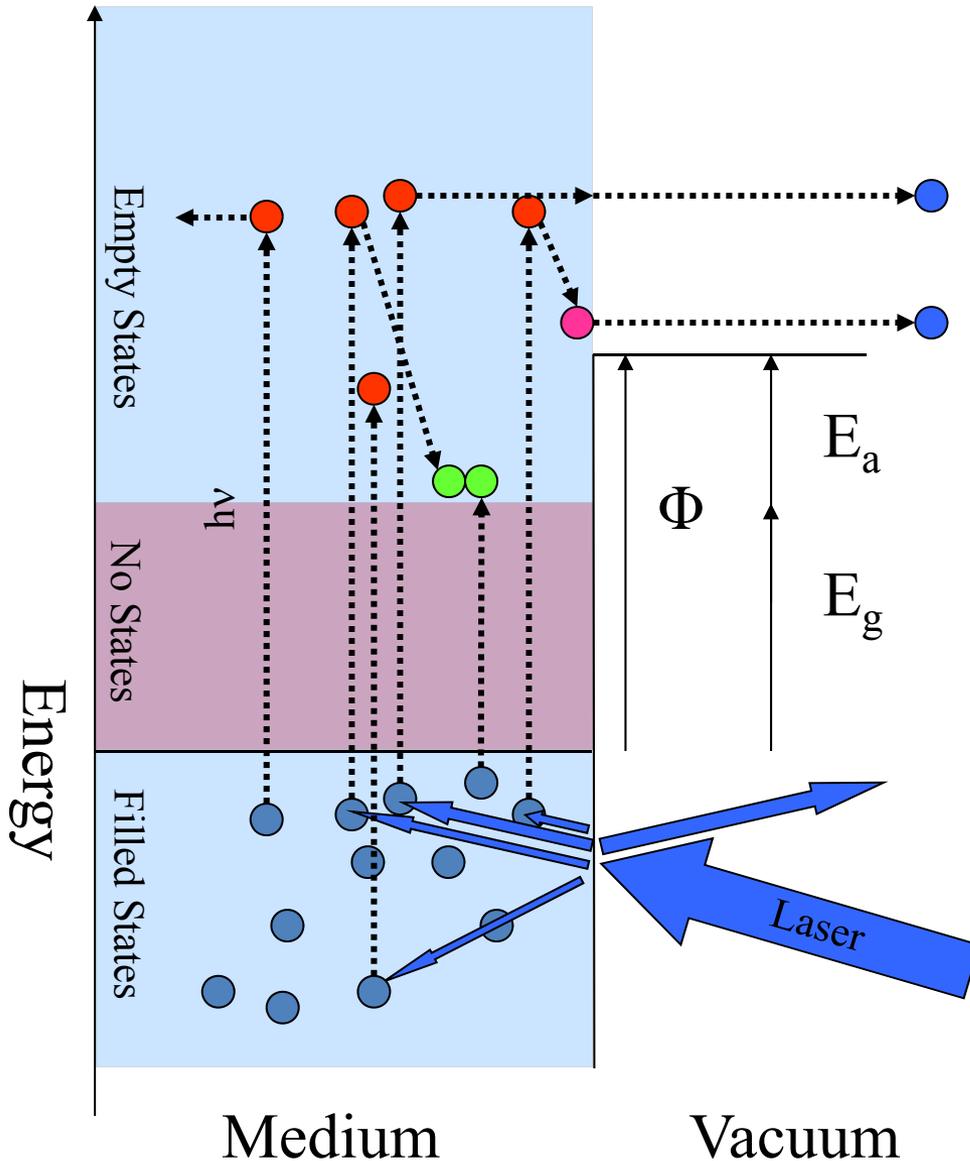
Common types:

Cs_2Te – QE ~7% @ 262 nm, Lifetime 100's of hrs

K_2CsSb – QE >4% @ 532 nm, Lifetime <10 hrs

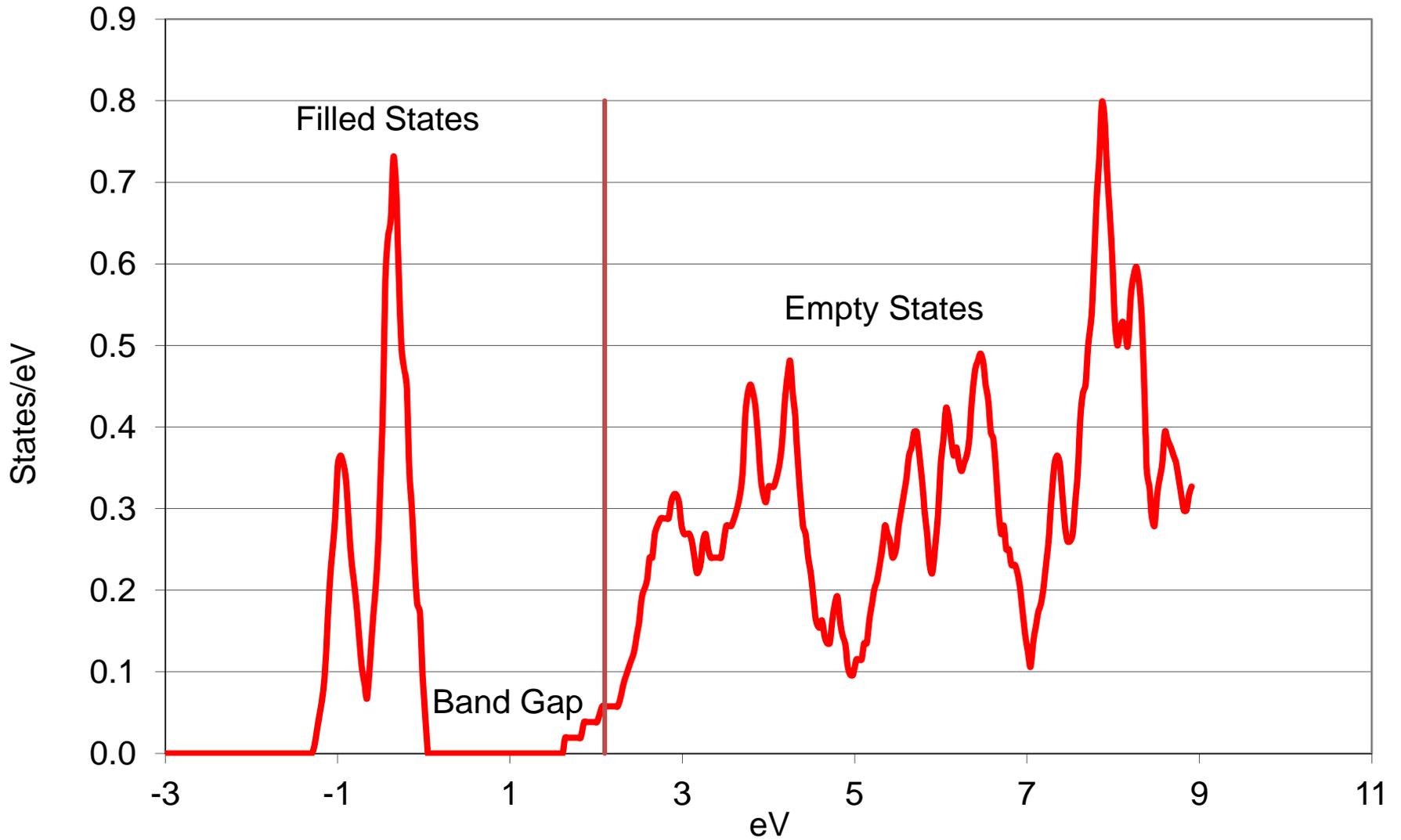
$\text{Cs}:\text{GaAs}$ – QE ~0.5% @ 800 nm (polarized), 6% @ 527 nm

Three Step Model - Semiconductors



- 1) Excitation of e^-
Reflection, Transmission, Interference
Energy distribution of excited e^-
- 2) Transit to the Surface
 e^- -lattice scattering
mfp ~ 100 angstroms
many events possible
 e^-e^- scattering (if $h\nu > 2E_g$)
Spicer's Magic Window
Random Walk
Monte Carlo
Response Time (sub-ps)
- 3) Escape surface
Overcome Electron Affinity

K_2CsSb DOS



A.R.H.F. Ettema and R.A. de Groot, Phys. Rev. B **66**, 115102 (2002)

K_2CsSb (Alkali Antimonides)

Work function 1.9eV, $E_g = 1.2$ eV

Very high QE for visible light (4% -12% @ 532 nm, >30% @ 355nm)

Deposited in 10^{-11} Torr vacuum

Typically sequential (Sb->K->Cs); Cs deposition used to optimize QE

Surface oxidation to create Cs-O dipole

Co-deposition increases performance in tubes

Cathodes stable in deposition systems (after initial cooldown)

Typical lifetime in an RF injector is measured in hours

Chemical poisoning is major cause of QE loss

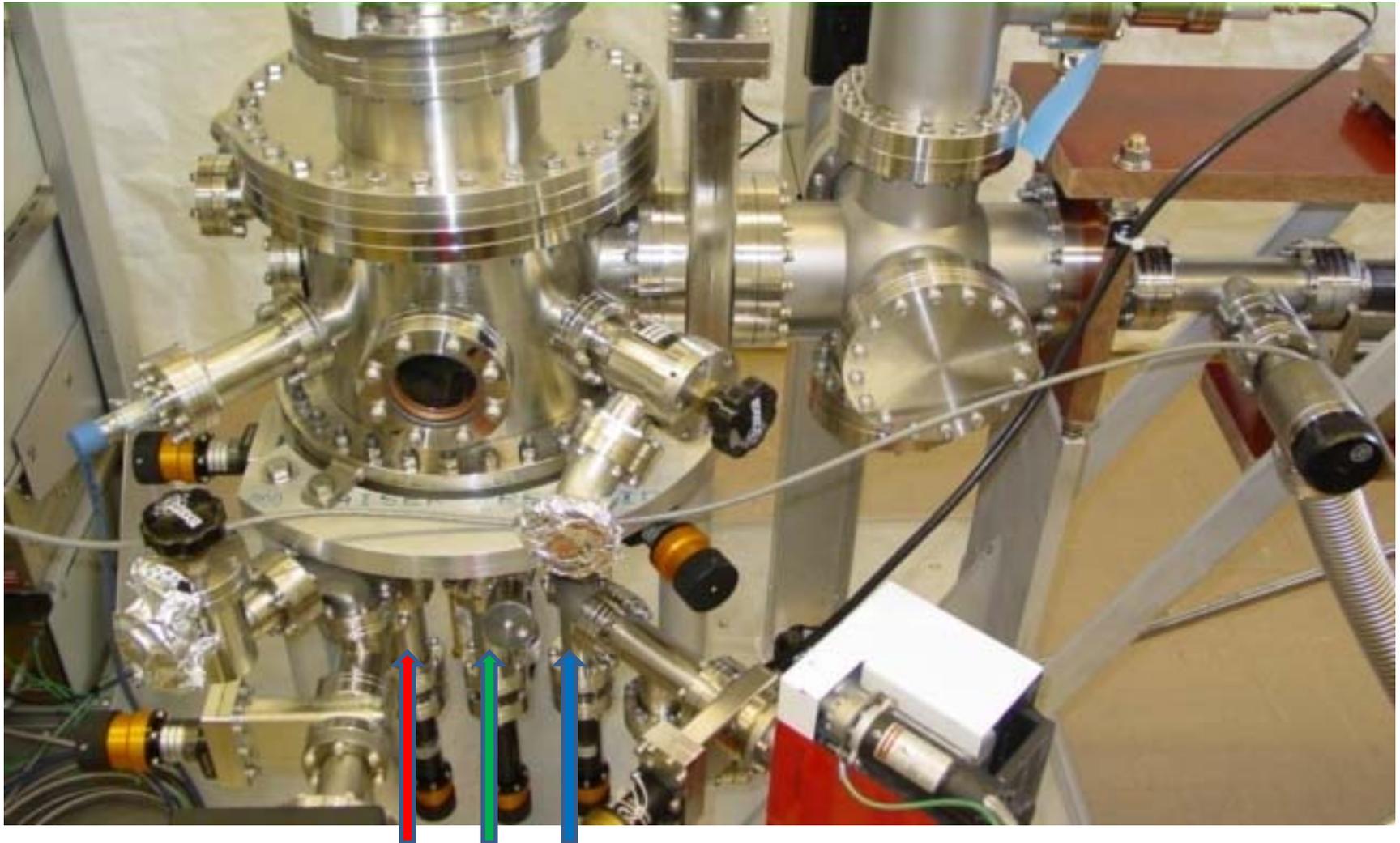
Cs-dispenser cathodes to allow in-situ rejuvenation being investigated

Improved vacuum should help (DC/Superconducting injectors)

D. H. Dowell *et al.*, *Appl. Phys. Lett.*, **63**, 2035 (1993)

C. Ghosh and B.P. Varma, *J. Appl. Phys.*, **49**, 4549 (1978)

Deposition System



Sb K Cs

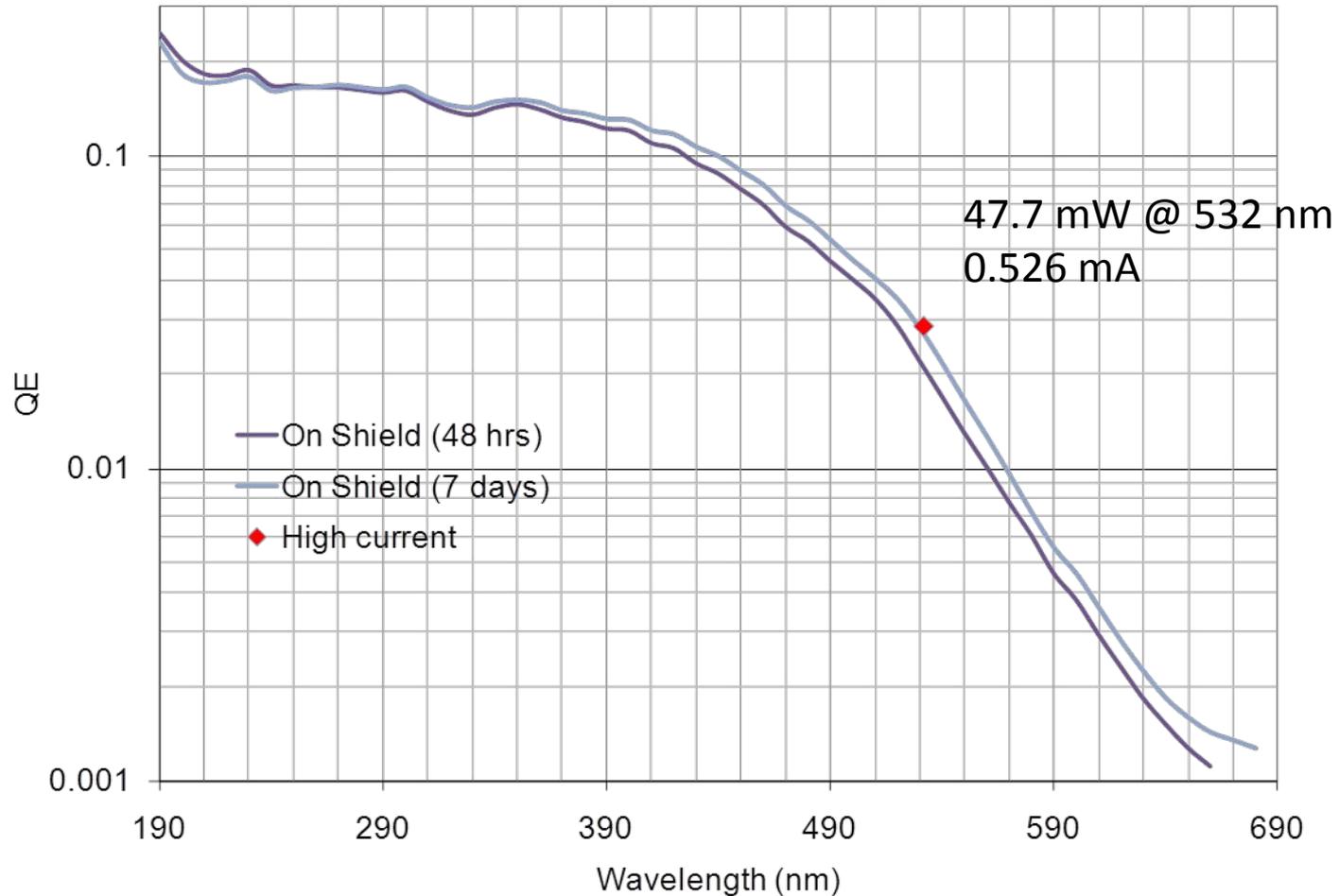
Sequential deposition with retractable sources (prevents cross-contamination)

Cathode mounted on rotatable linear-motion arm

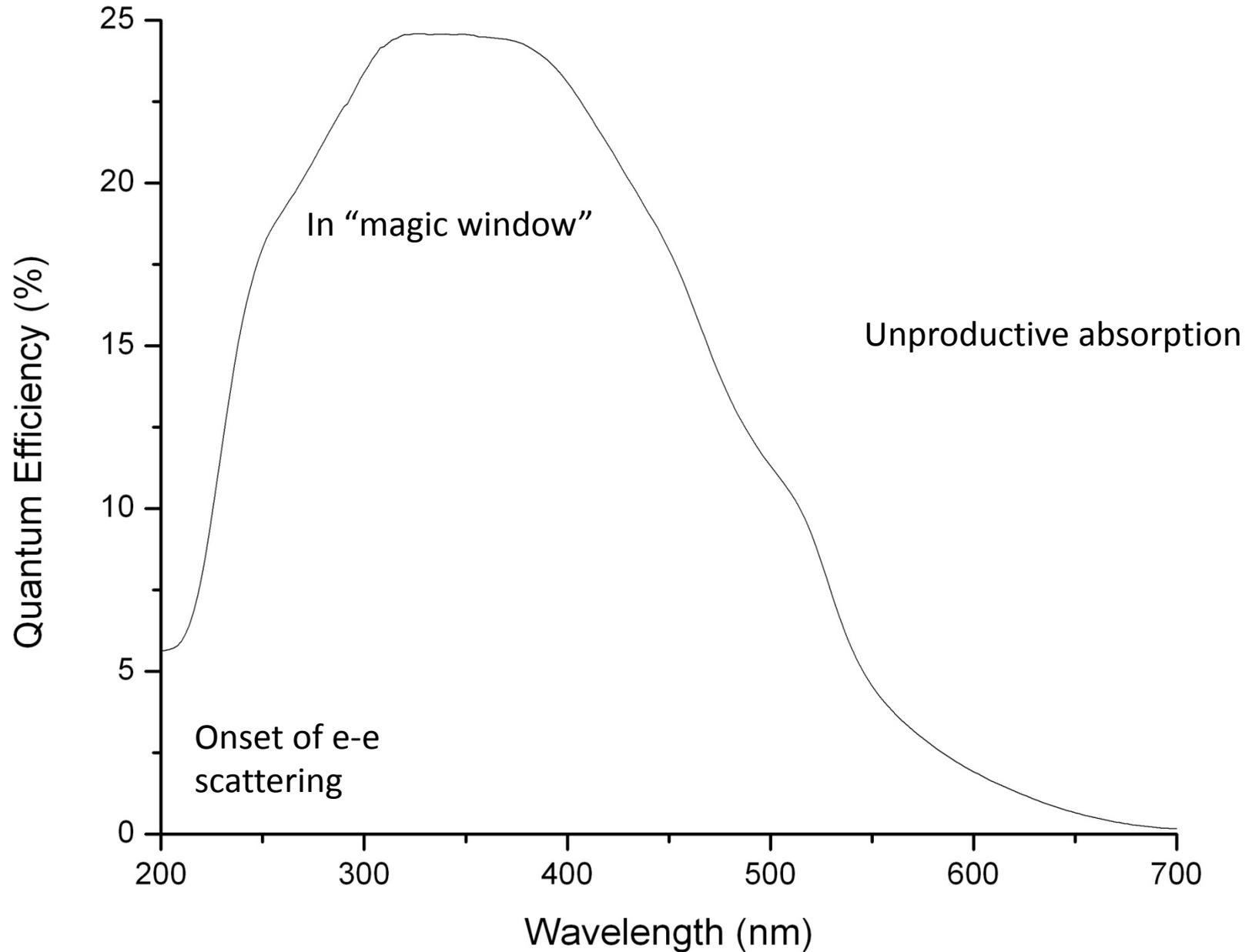
Typical vacuum 0.02 nTorr (0.1 nTorr during Sb deposition)

K_2CsSb Performance

Deposition Chamber, no oxidation



Spectral Response – Bi-alkali



Cs₂Te

Most common cathode for ~1mA injectors

Work function 3.6eV, E_g= 3.2 eV

Good QE for UV light (Max >20%, Average ~7% @ 262 nm)

Deposited in 10⁻¹¹ Torr vacuum

Typically sequential (Te->Cs); Cs used to optimize QE

Co-deposition increases performance

Typical lifetime in an RF injector is measured in weeks-months

Chemical poisoning (and Cs loss?) is major cause of QE loss

Improve vacuum should help (DC/Superconducting injectors)

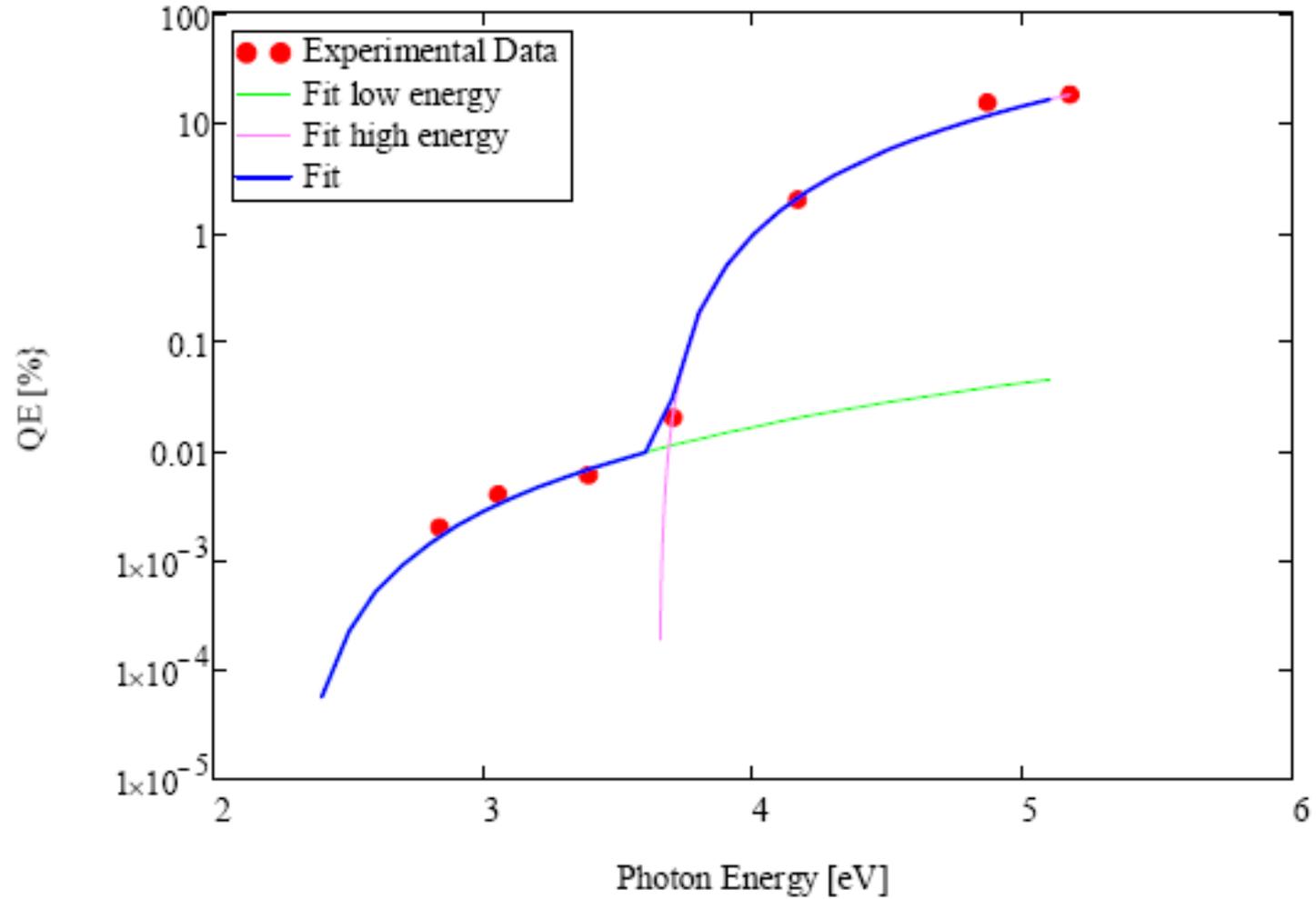
Can be shipped in vacuum suitcase

D. Sertore *et al.*, PAC07, 2760

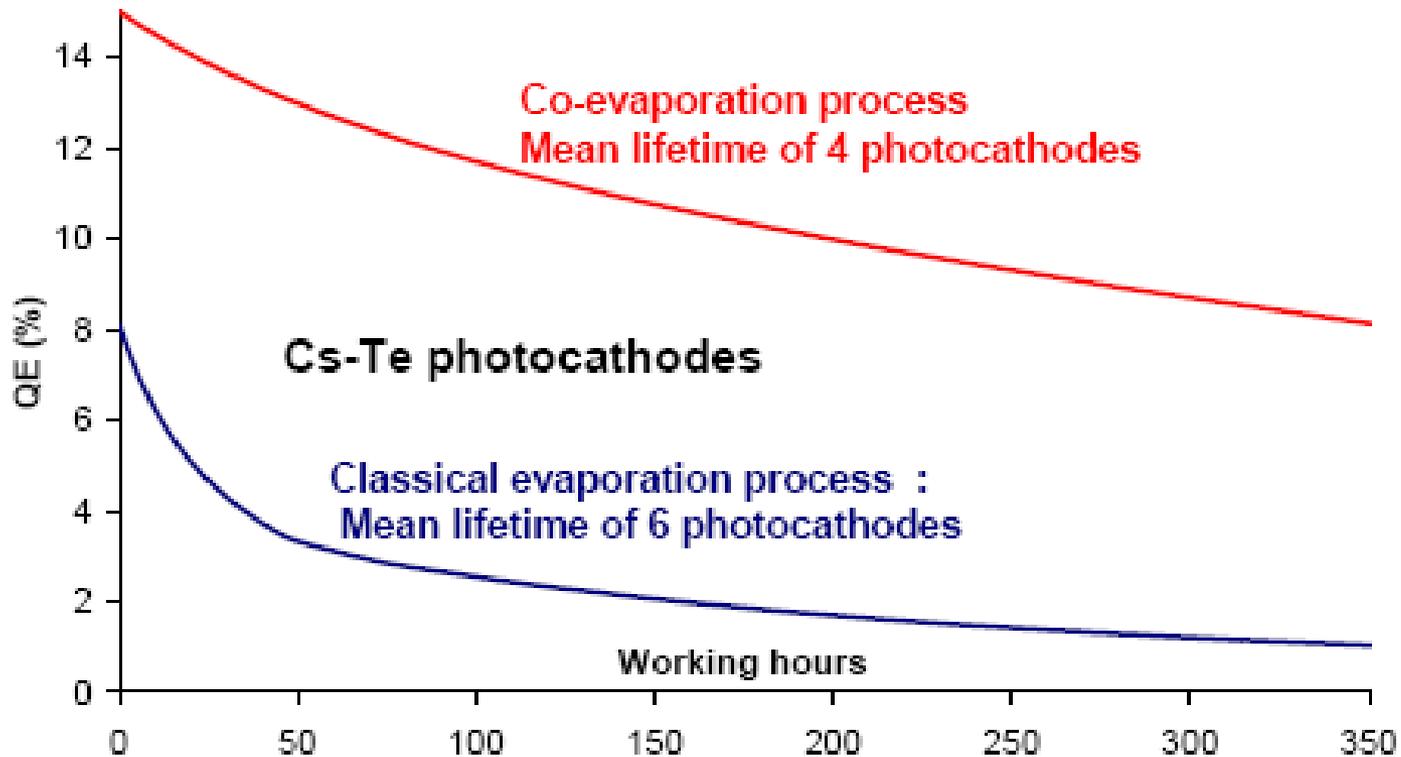
G. Suberlucq, EPAC04, 64

F. Banfi *et al.*, FEL07, 572

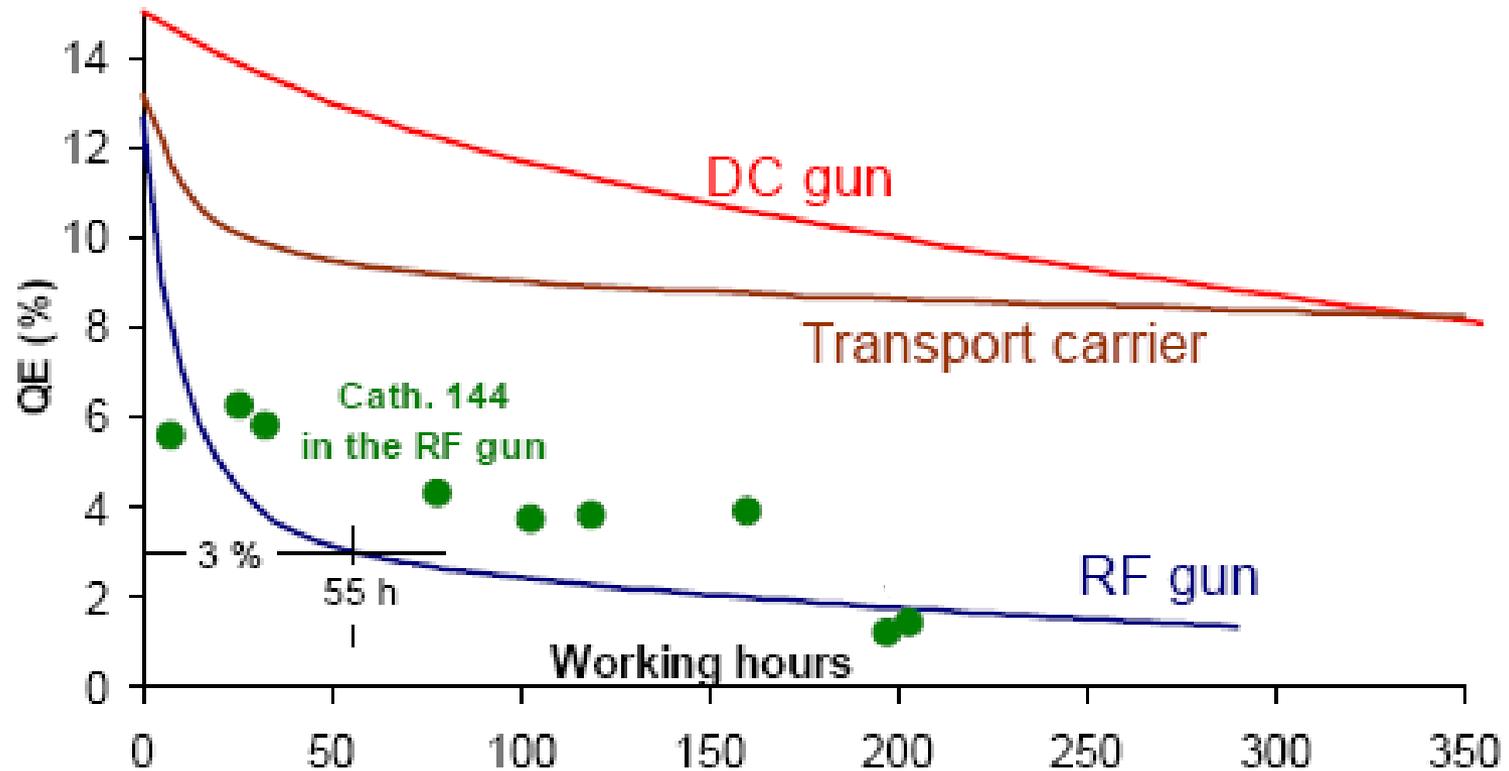
Spectral Response



Lifetime in DC gun



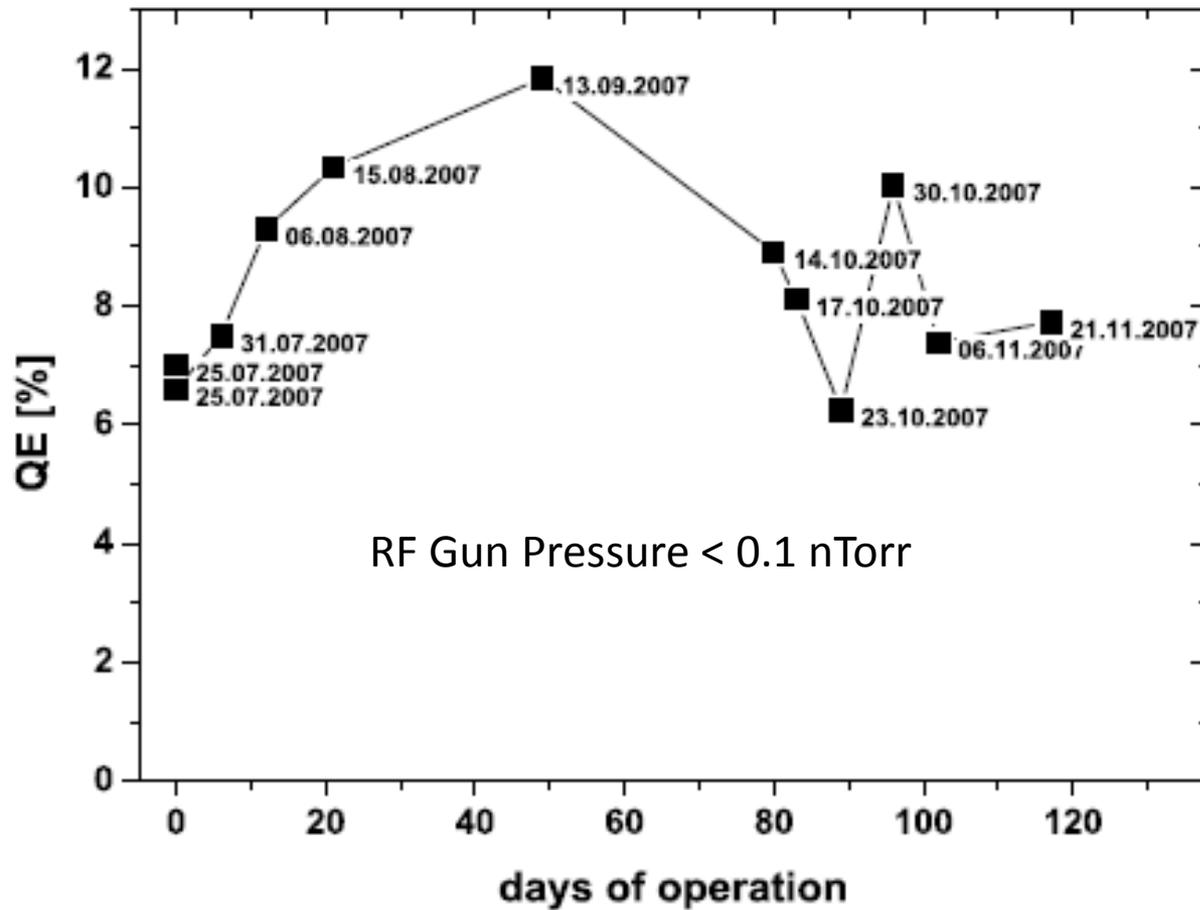
Lifetime in RF gun



DC Gun Pressure <0.1 nTorr

RF Gun Pressure ~nTorr

Lifetime in RF gun FLASH/INFN-LASA



Cesiated GaAs

Cathode of choice for DC injectors

Can produce polarized electrons (strained superlattice)

Negative Electron Affinity ($\sim -0.2\text{eV}$), $E_g = 1.4\text{ eV}$

Polarized QE: 0.5% @ 800 nm

Unpolarized QE: 6% @ 527 nm (max > 15%)

Response time is $\sim 100\text{ ps}$ for 800nm, $\sim 1\text{ ps}$ for 527 nm

Preparation:

- Start with clean GaAs wafer (Atomic H clean if necessary)

- Deposit Cs monolayer, expose to oxidizing gas (O_2 or NF_3)

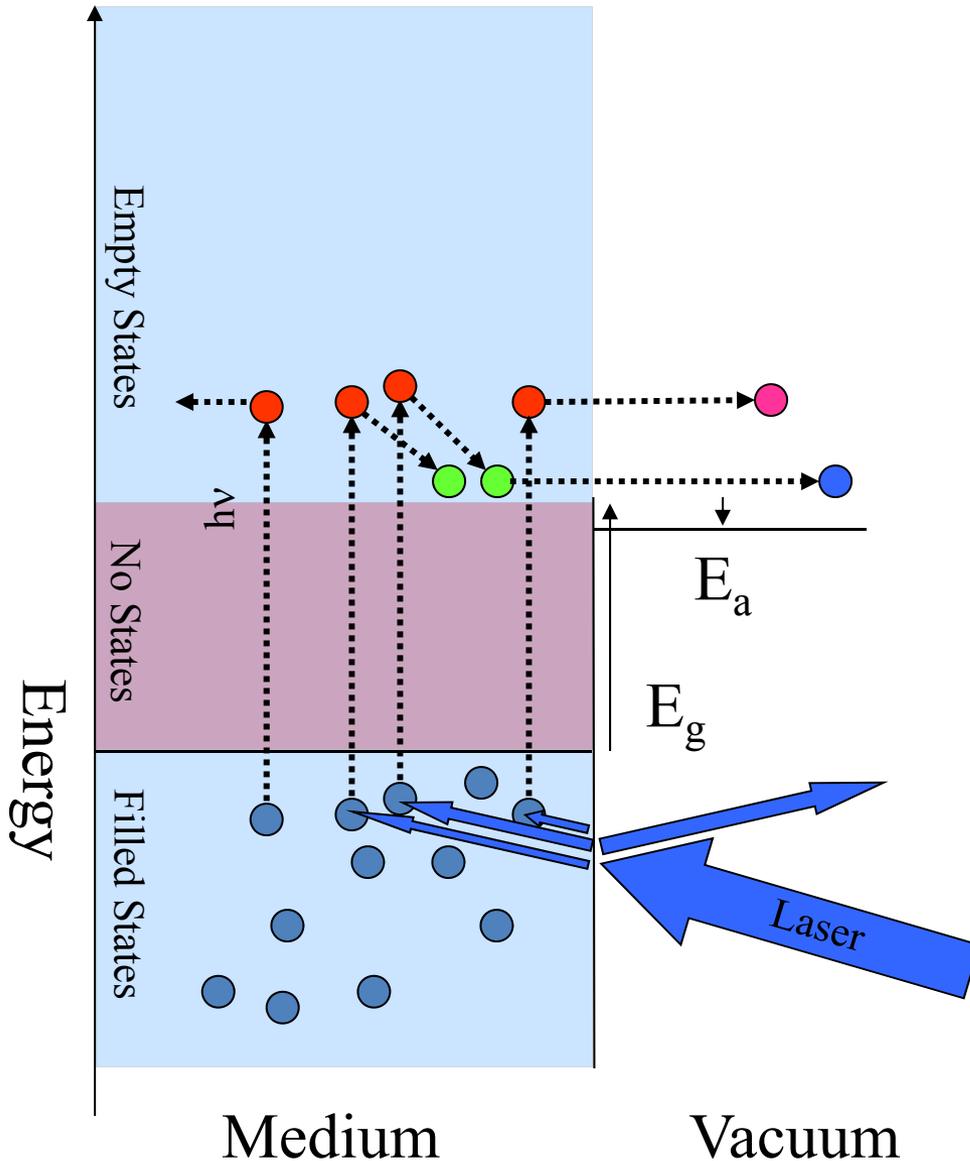
- Alternate while monitoring QE

Typical lifetime in an DC injector is 100-500C (can recesiate)

- Ion back-bombardment is the major source of QE loss

- Superconducting Injectors may help

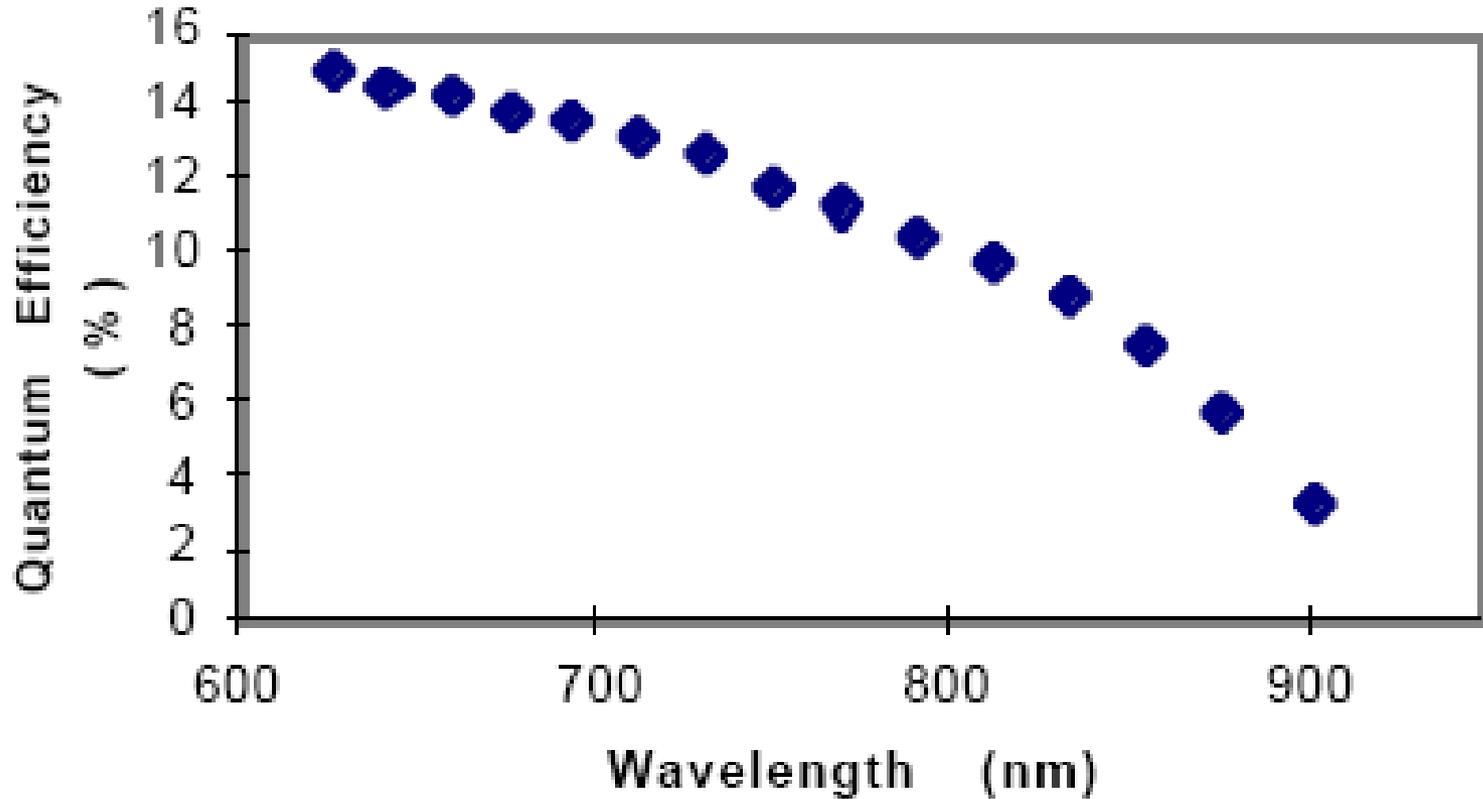
Three Step Model – NEA Semiconductors



- 1) Excitation of e^-
Reflection, Transmission,
Interference
- 2) Transit to the Surface
 e^- -lattice scattering
thermalization to CBM
diffusion length can be $1\mu\text{m}$
recombination
Random Walk
Monte Carlo
Response Time (10-100 ps)
- 3) Escape surface

Spectral Response of Cesiumated Bulk GaAs

In Test Chamber

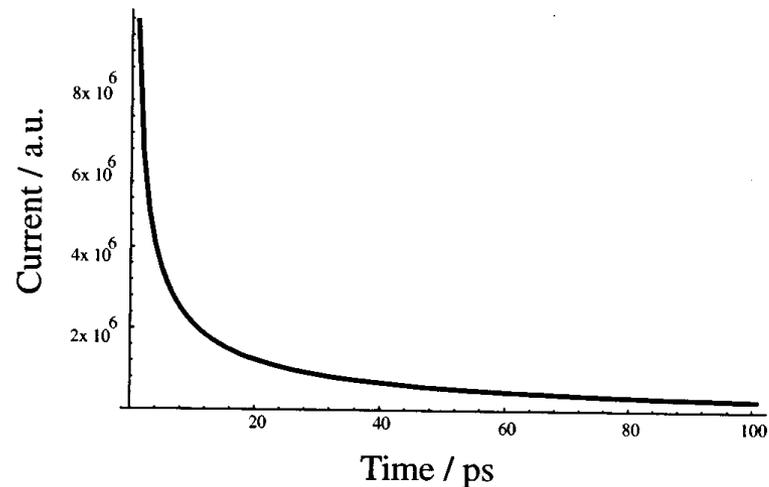
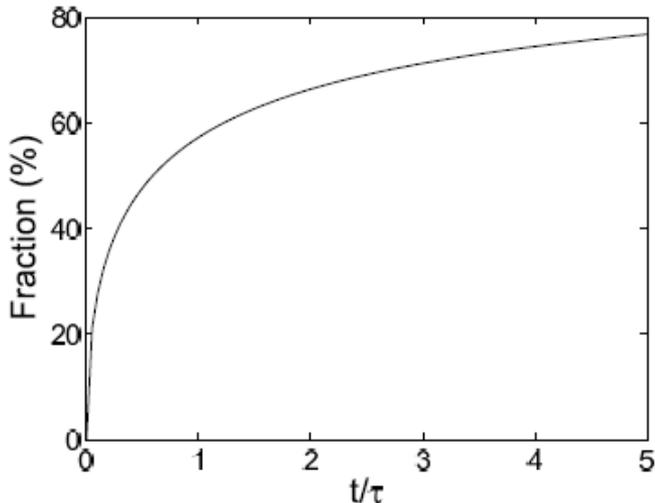


Temporal Response Measurements

- High quality measurements require an RF deflection cavity
- Three measurements with cavities:
 - Aleksandrov et al., Phys. Rev. E 51, 1449 (1995)
Had insufficient temporal resolution
 - Hartmann et al., JAP 86, 2245 (1999)
Studied only near the bandgap
 - Bazarov et al., JAP 103, 054901 (2008), and PRST-AB 11, 040702 (2008)
Used two techniques, and measured versus λ

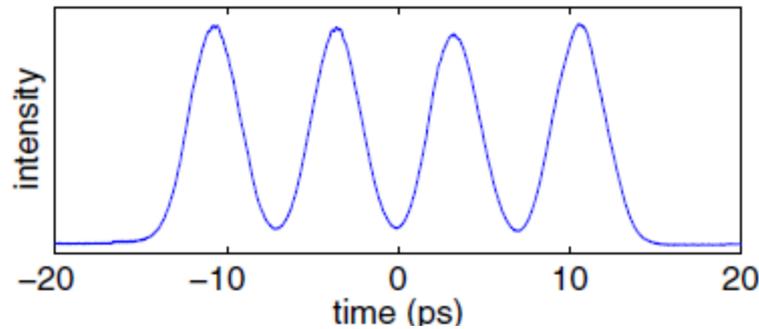
Temporal Response

- A solution to the diffusion equation for a delta-function optical pulse gives a fast initial component and a long tail. 57% of the pulse is contained within $t/\tau = 1$, with $\tau = 1/\alpha^2 D$; α is the absorption coefficient, and D is the diffusion constant.

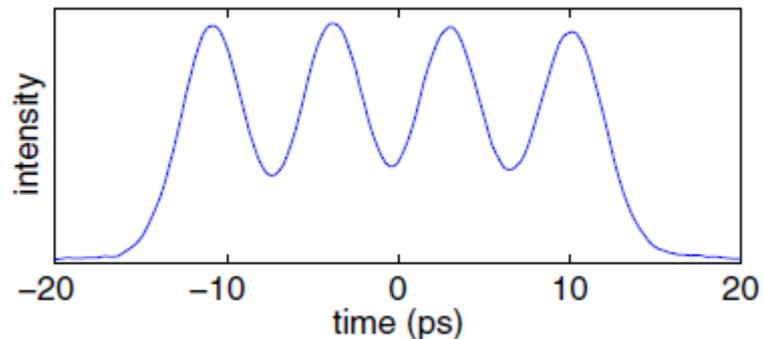


GaAs is prompt at 520 nm

| Wavelength | 200 kV Gun Voltage | 250 kV Gun voltage |
|------------|--------------------|--------------------|
| 860 nm | 76 +/- 26 ps | 69 +/- 22 ps |
| 785 nm | 11.5 +/- 1.2 ps | 9.3 +/- 1.1 ps |
| 710 nm | 5.8 +/- 0.5 ps | 5.2 +/- 0.5 ps |
| 520 nm | ≤ 1 ps | |
| 460 nm | ≤ 0.14 ps | |

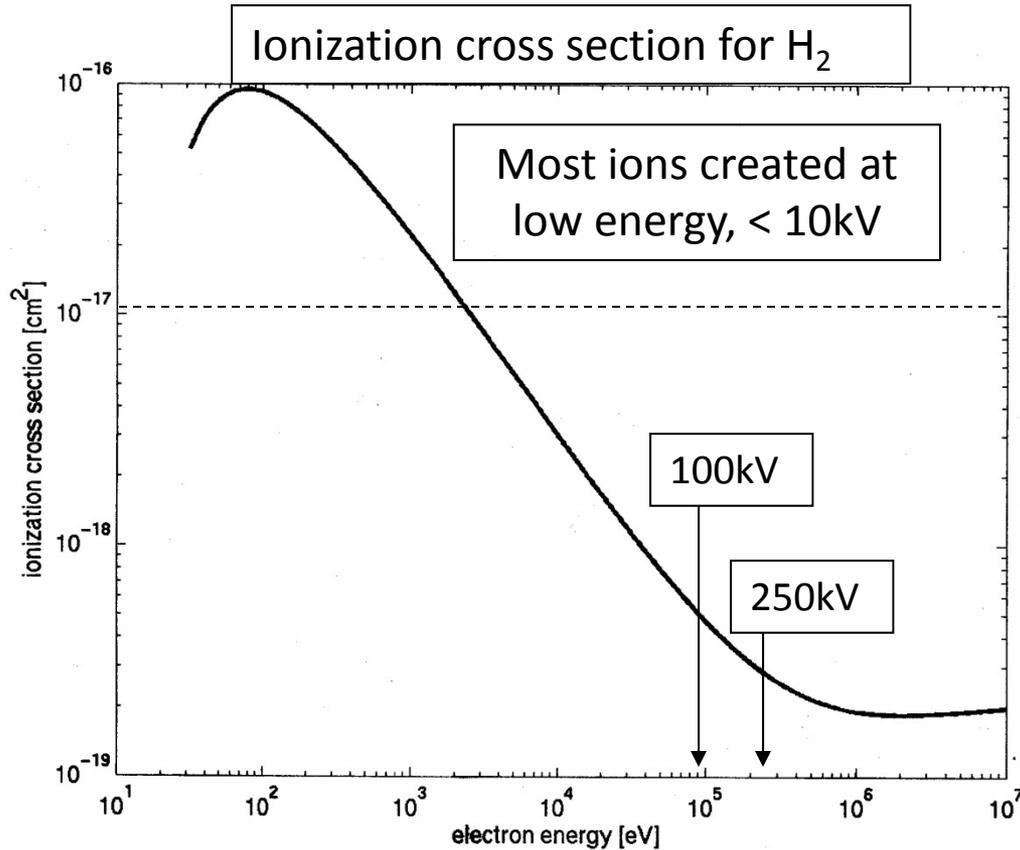


Cross correlation
measurement of 520 nm
laser beam

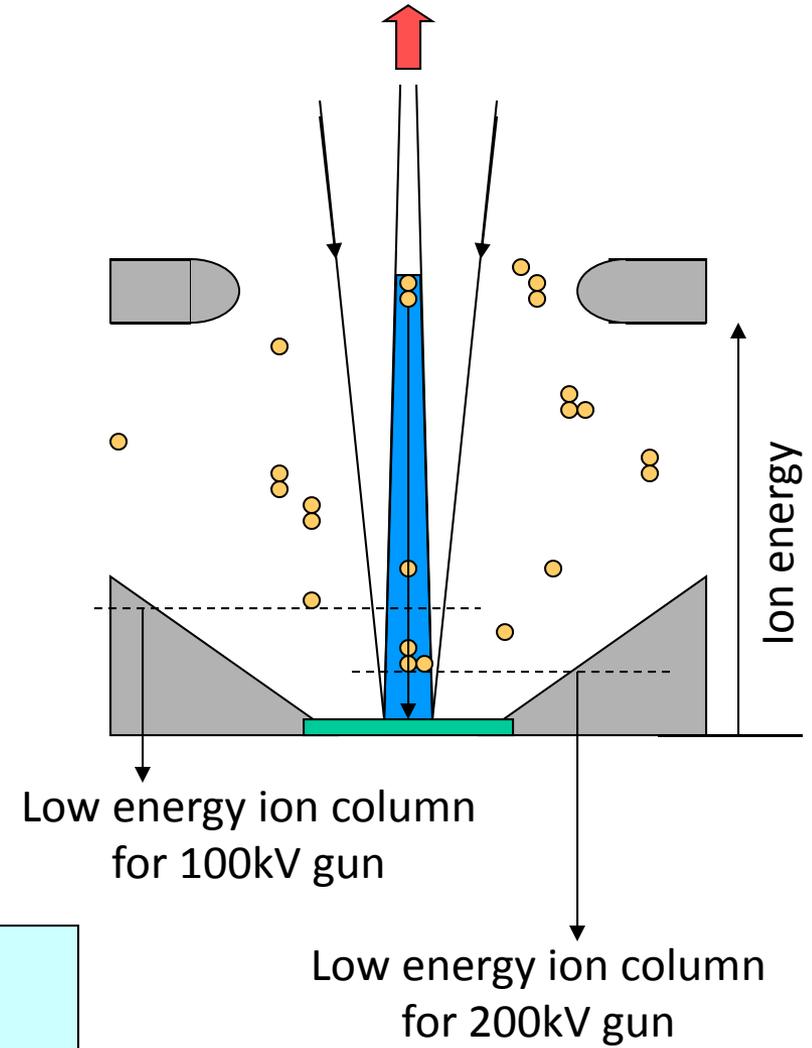


RF deflection cavity
measurement of electron
beam

Improve Lifetime with Higher Bias Voltage?



Hypothesis: Double the gun voltage, halve the # of "bad" ions, improve lifetime by 2



Slide courtesy of M. Poelker, Jlab

Photocathode Summary

Still a lot of voids....

| <i>Metal Cathodes</i> | <i>Wavelength & Energy:</i> λ_{opt} (nm), $\hbar\omega$ (eV) | <i>Quantum Efficiency</i> (electrons per photon) | <i>Vacuum for 1000 Hr Operation</i> (Torr) | <i>Work Function,</i> ϕ_w (eV) | <i>Thermal Emittance</i> (microns/mm(rms)) | |
|-----------------------|--|---|---|--|---|--|
| | | | | | <i>Eqn. [3]</i> | <i>Expt.</i> |
| Bare Metal | | | | | | |
| Cu | 250, 4.96 | 1.4×10^{-4} | 10^{-9} | 4.6 [34] | 0.5 | 1.0±0.1 [39] 1.2±0.2 [40] 0.9±0.05 [3] |
| Mg | 266, 4.66 | 6.4×10^{-4} | 10^{-10} | 3.6 [41] | 0.8 | 0.4±0.1 [41] |
| Pb | 250, 4.96 | 6.9×10^{-4} | 10^{-9} | 4.0 [34] | 0.8 | ? |
| Nb | 250, 4.96 | $\sim 2 \times 10^{-5}$ | 10^{-10} | 4.38 [34] | 0.6 | ? |
| Coated Metal | | | | | | |
| CsBr:Cu | 250, 4.96 | 7×10^{-3} | 10^{-9} | ~ 2.5 | ? | ? |
| CsBr:Nb | 250, 4.96 | 7×10^{-3} | 10^{-9} | ~ 2.5 | ? | ? |

...Waiting to be filled with numbers

| Cathode Type | Cathode | Typical Wavelength, λ_{opt} (nm), (eV) | Quantum Efficiency (electrons per photon) | Vacuum for 1000 Hrs (Torr) | Gap Energy + Electron Affinity, $E_A + E_G$ (eV) | Thermal Emittance (microns/mm(rms)) | |
|----------------------|---------------------------------------|--|---|----------------------------|--|-------------------------------------|----------------|
| | | | | | | Eqn. [7] | Expt. |
| PEA: Mono-alkali | Cs ₂ Te | 211, 5.88 | ~0.1 | 10 ⁻⁹ | 3.5 [42] | 1.2 | 0.5±0.1 [35] |
| | | 264, 4.70 | - | - | " | 0.9 | 0.7±0.1 [35] |
| | | 262, 4.73 | - | - | " | 0.9 | 1.2 ±0.1 [43] |
| | Cs ₃ Sb | 432, 2.87 | 0.15 | ? | 1.6 + 0.45 [42] | 0.7 | ? |
| | K ₃ Sb | 400, 3.10 | 0.07 | ? | 1.1 + 1.6 [42] | 0.5 | ? |
| PEA: Multi-alkali | Na ₃ Sb | 330, 3.76 | 0.02 | ? | 1.1 + 2.44 [42] | 0.4 | ? |
| | Li ₃ Sb | 295, 4.20 | 0.0001 | ? | ? | ? | ? |
| | Na ₂ K ₂ Sb | 330, 3.76 | 0.1 | 10 ⁻¹⁰ | 1+1 [42] | 1.1 | ? |
| | (Cs)Na ₃ K ₂ Sb | 390, 3.18 | 0.2 | 10 ⁻¹⁰ | 1+0.55 [42] | 1.5 | ? |
| | K ₂ CsSb | 543, 2.28 | 0.1 | 10 ⁻¹⁰ | 1+1.1 [42] | 0.4 | ? |
| NEA | GaAs(Cs,F) | 532, 2.33 | ~0.1 | ? | 1.4±0.1 [42] | 0.8 | 0.44±0.01 [44] |
| | | 860, 1.44 | - | ? | " | 0.2 | 0.22±0.01 [44] |
| | GaN(Cs) | 260, 4.77 | - | ? | 1.96 + ? [44] | 1.35 | 1.35±0.1 [45] |
| | GaAs(1-x)Px x~0.45 (Cs,F) | 532, 2.33 | - | ? | 1.96+? [44] | 0.49 | 0.44±0.1 [44] |
| S-1 | Ag-O-Cs | 900, 1.38 | 0.01 | ? | 0.7 [42] | 0.7 | ? |

Laser Photo-Field Emission from Needle

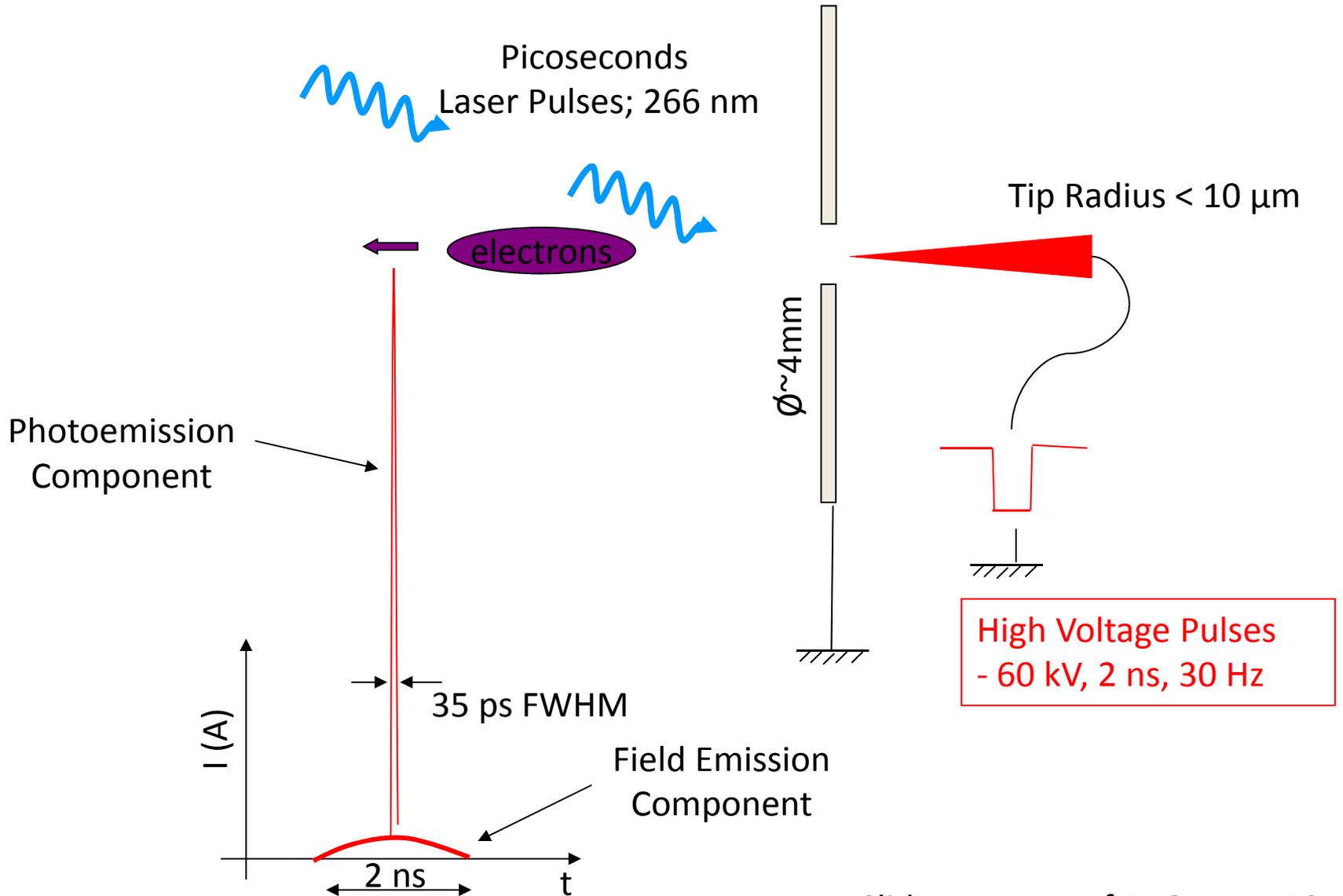
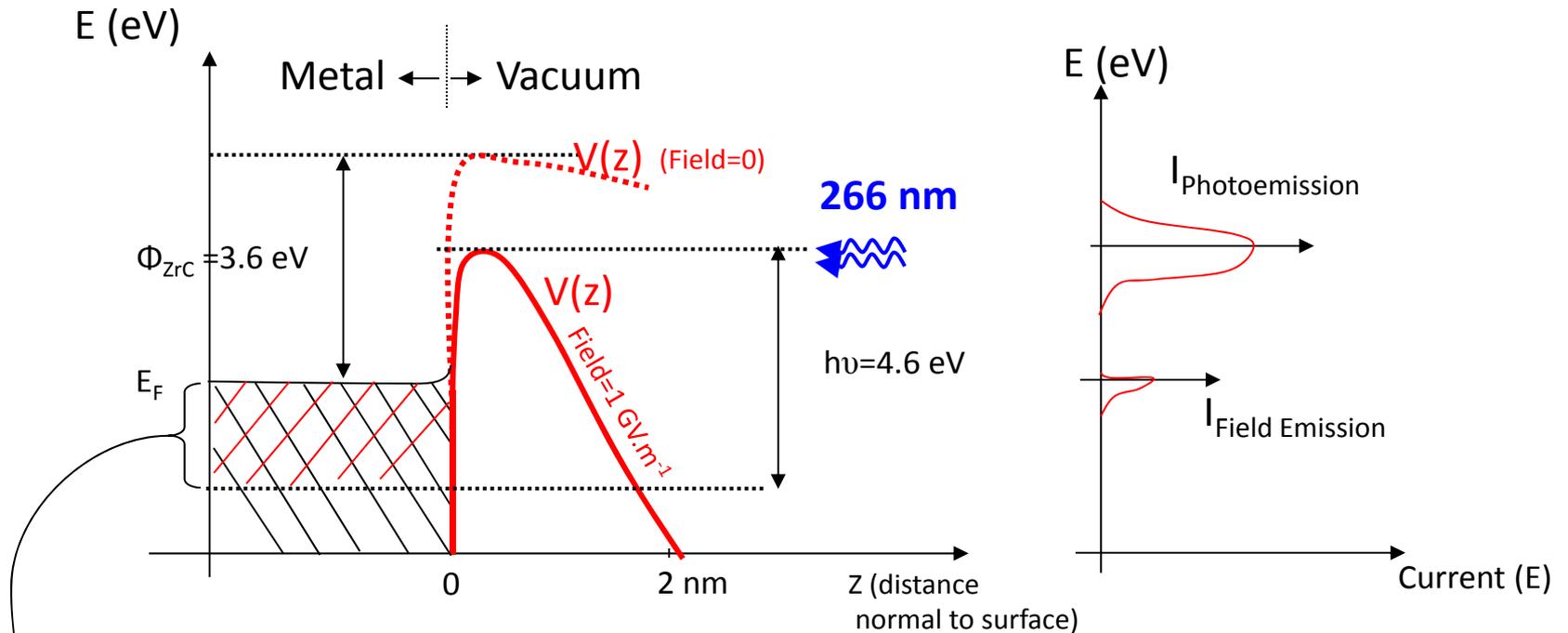


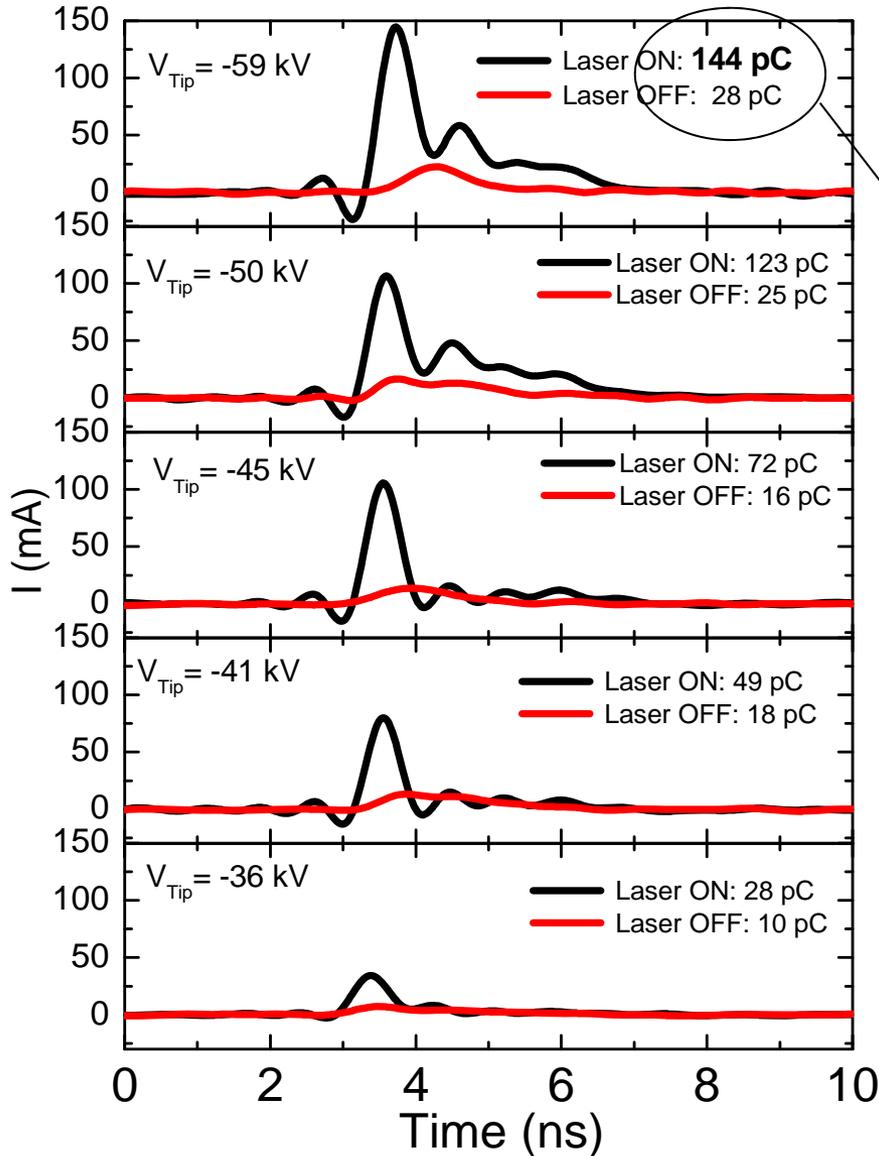
Photo-Field Emission Principle

Schottky Effect \rightarrow Larger Electron Reservoir for Photoemission \rightarrow Higher Quantum Efficiency



Energy range from where electrons can be directly photo-emitted !

Quantum Efficiency depends on E_{local}



Higher Tip Voltage (E_{Local})



Larger Quantum Efficiency

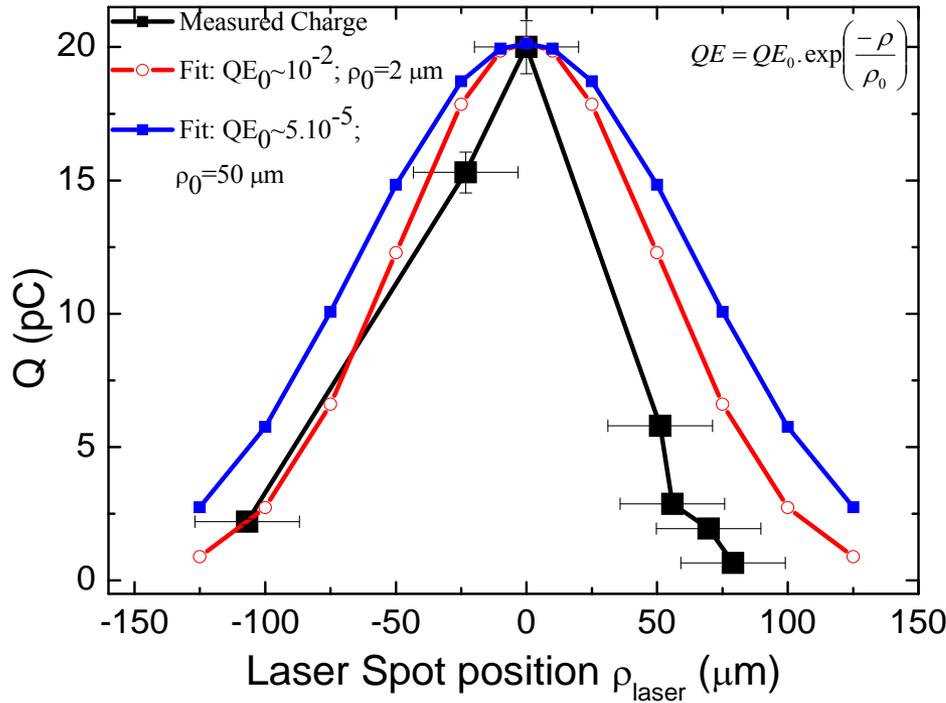
144 pC at $6 \mu\text{J}$ (266 nm)
Q.E. $\sim 10^{-4}$

BUT

$QE_{\text{apex}} \gg QE_{\text{shank}}$

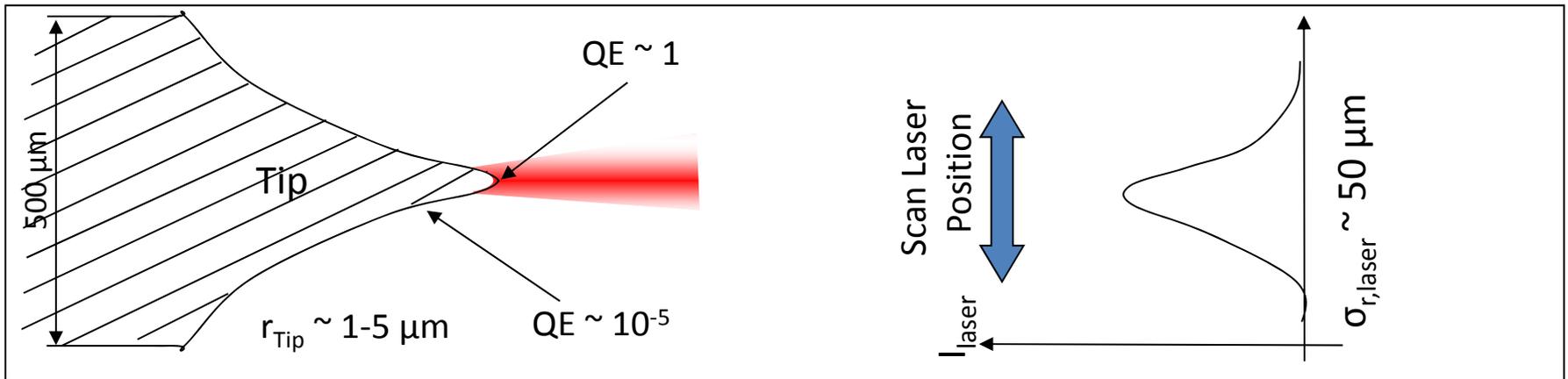
Laser: $6 \mu\text{J} / \sigma_{t,\text{laser}}=16 \text{ ps} / \sigma_{r,\text{laser}}=85 \mu\text{m} / 30 \text{ Hz} / 266 \text{ nm}$

Photo-Field Emission Emitting Area

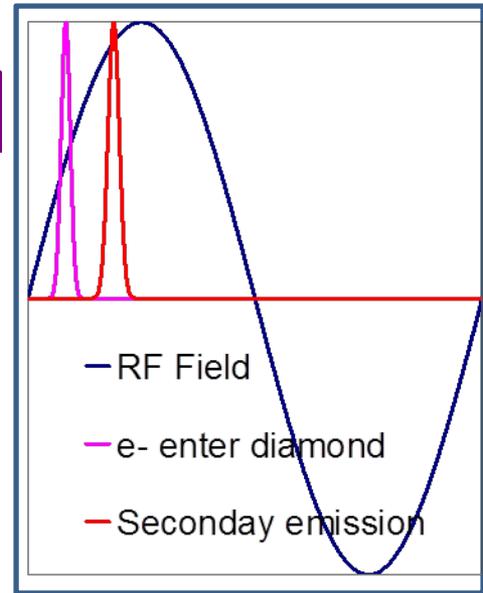
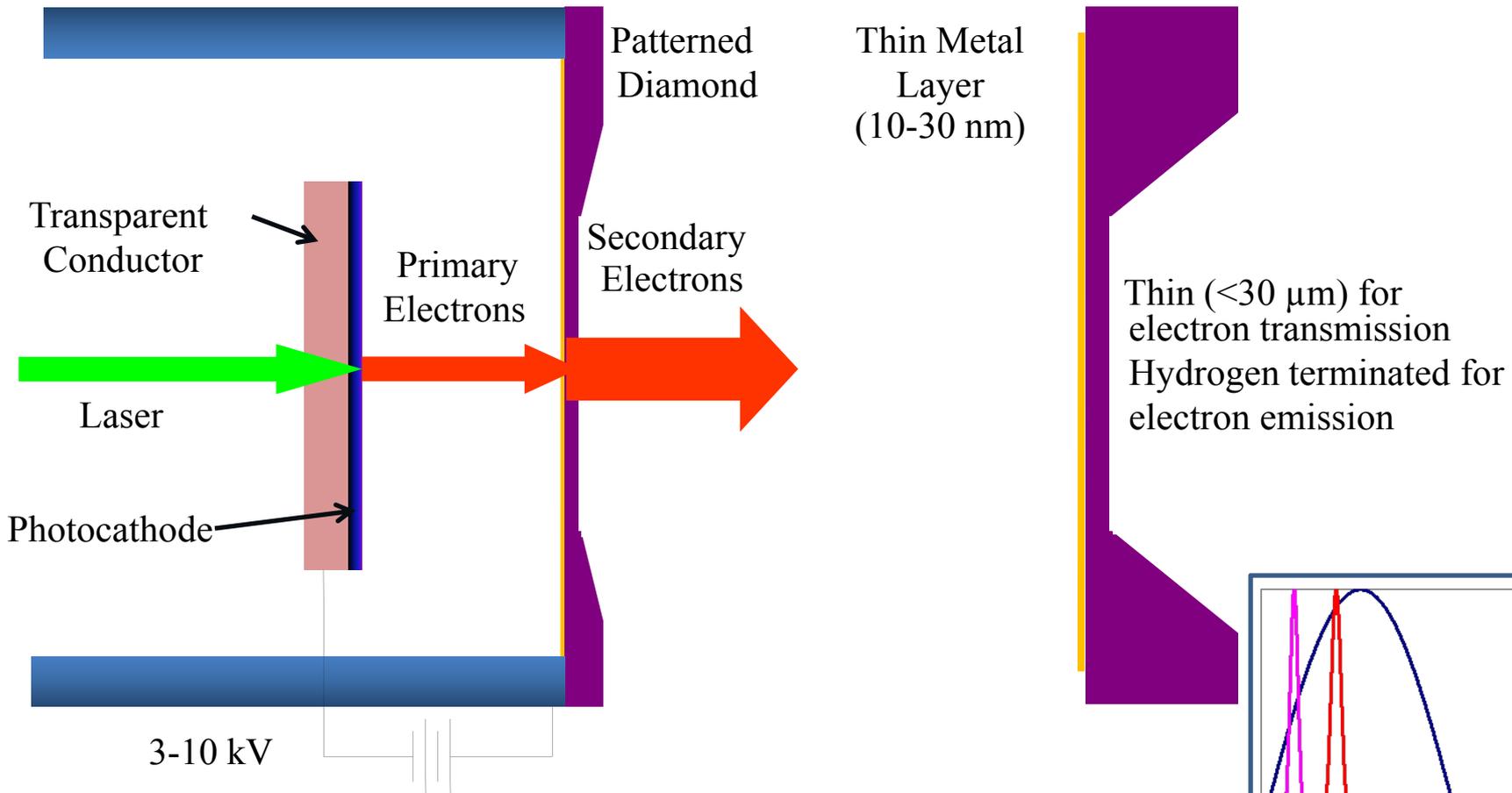


Non uniform QE distribution along Tip Shanks !

Exp. Cond.:
 266 nm; 3 μJ ; $\sigma_{r,\text{laser}} \sim 50 \mu\text{m}$
 $\sigma_{z,\text{laser}} \sim 16 \text{ ps}$; $V_{\text{Tip}} = -32 \text{ kV}$



Diamond Amplifier Concept



Electron saturation velocity in Diamond is $\sim .2 \mu\text{m}/\text{ps}$
Takes 150 ps to go $30 \mu\text{m} = 40$ degrees of RF
Electrons must exit diamond in time to escape injector
Irregularity of surface will cause bunch spreading

Diamond Amplifier Concept

Advantages

Secondary current can be **>300x** primary current

Lower laser power

Higher average currents

Diamond acts as vacuum barrier

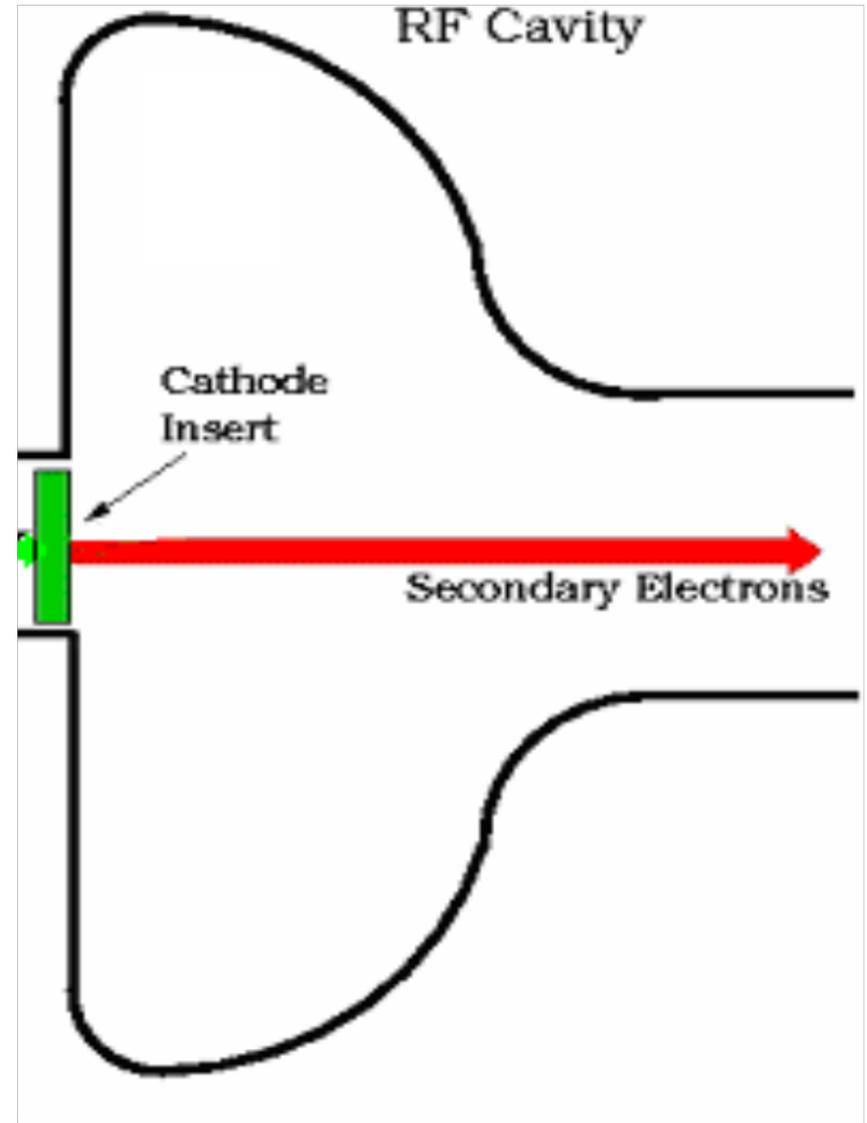
Protects cathode from cavity vacuum and ion bombardment

Protects cavity from cathode (prevents Cs migration)

Should improve cathode lifetime

e^- thermalize to near conduction-band minimum

Minimize thermal emittance



Online Resources

Good discussion of work function:

<http://www.philiphofmann.net/surflec3/surflec015.html>

Materials properties database:

<http://mits.nims.go.jp/matnavi/>

Accelerator publications:

www.JACoW.org & Physical Review Special Topics Accelerators and Beams

Semiconductor Physics (Don't laugh... well, ok laugh a little - but it is a great site)

<http://britneyspears.ac/lasers.htm>

Hamamatsu PMT Handbook:

http://sales.hamamatsu.com/assets/pdf/catsandguides/PMT_handbook_v3aE.pdf